Wireless System-on-Chip and System-on-Package Design for Biomedical Applications

by

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A thesis submitted to the Department of Electronics in partial fulfillment of the requirements for the degree of Doctor of Philosophy in Engineering.

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Ottawa, Canada

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Abstract

In this thesis, novel wireless System-on-Chip (SoC) and System-on-Package (SoP) have been developed for biomedical applications. A radiation dose measurement system for the treatment of cancer patients is the chosen application. Typically this measurement requires a wired sensor which uses the change in Radiation Field Effect Transistor (RADFET) threshold voltage before and after the radiation exposure to measure the dose. While these dosimeters have good sensitivity, the wires employed deflect and scatter the radiation away from the targeted region during the irradiation process. To avoid these ill effects and to relieve patients from a cluster of wires on their bodies, a short range radio for transmitting the sensor data is proposed. The complete system is highly compact and small in size. The SoC part includes the design of a 5.2 GHz transmitter (TX) with a unique on-chip antenna. The on-chip antenna performs double duty and acts as an inductor for the TX Voltage Controlled Oscillator (VCO). The SoC designed in IBM CMOS 0.13 um process occupies only 1.5 mm² of chip space and successfully transmits the sensor data up to 2 m of range with a power consumption of 3 mW. Similarly, a receive side on-chip antenna has also been designed which is conjugately matched to the LNA over a wide bandwidth.

In order to package the TX chip, Low Temperature Co-fired Ceramic (LTCC) technology in employed. Custom LTCC packages provide high levels of integration and reduction in size due to their embedded 3D-structured passives. An efficient SoP has been designed in Ferro A6-S LTCC, accommodating the sensor and TX chips in tailor-made cavities. It has an LTCC antenna integrated to the TX chip through isolating buffer amplifiers. The SoP design increases the communication range to 75 m with the efficient antenna; however the power consumption also rises to 38 mW due to the buffers. To reduce power consumption and still use an efficient antenna, a novel LTCC package is designed where the package antenna is fed electromagnetically from the TX's on-chip antenna. This wireless coupling eliminates the need for buffer amplifiers, bond wires and matching circuit elements, and hence improves the communication range with no additional power consumption. As an enhancement of SoP, ferrite LTCC is also investigated for tuneable and reconfigurable antennas. The introduction of ferrite material into the LTCC package permits control of the devices made from it. Completely embedded transformers in ferrite LTCC are designed and fabricated for material characterization. These transformers are also utilized as biasing circuits for the antennas. A measured tuning range of up to 550 MHz is observed from ferrite LTCC based patch antennas. As a result of embedding the bias windings, the typically required external fields of the order of 1000 Oe to tune ferrite based antennas have been reduced to the order of 50 Oe. This makes ferrite LTCC a suitable candidate for tuneable and re-configurable wireless SoP.
Acknowledgements

First of all, I wish to thank God for giving me this opportunity to pursue my educational goals. Then, I wish to express my sincere appreciation to my thesis supervisor, Dr. Langis Roy for his immense support, encouragement and continuous guidance throughout this thesis project. I consider myself fortunate to have him as my supervisor, as he has not only taught me technical things but has also coached me in numerous issues related to the professional life. He has inspired me with his dedication to work and with his positive attitude towards life. I thank him for all the knowledge he has imparted and for all the time he has dedicated to this thesis.

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I dedicate this thesis to the memories of my loving mother, who believed in me right from the start. Her thoughts have always motivated me in hard times.
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<th>Description</th>
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<tbody>
<tr>
<td>(\lambda)</td>
<td>any wavelength in general</td>
</tr>
<tr>
<td>(\lambda_0)</td>
<td>wavelength in free space</td>
</tr>
<tr>
<td>(\lambda_g)</td>
<td>wavelength in dielectric medium (guided wavelength)</td>
</tr>
<tr>
<td>(\Omega)</td>
<td>ohm</td>
</tr>
<tr>
<td>(\alpha)</td>
<td>attenuation constant</td>
</tr>
<tr>
<td>(\beta)</td>
<td>phase constant</td>
</tr>
<tr>
<td>(\Delta l)</td>
<td>feed gap length</td>
</tr>
<tr>
<td>(\sigma)</td>
<td>conductivity</td>
</tr>
<tr>
<td>(\pi)</td>
<td>pi</td>
</tr>
<tr>
<td>(\omega)</td>
<td>angular frequency</td>
</tr>
<tr>
<td>dB</td>
<td>decibel</td>
</tr>
<tr>
<td>dBi</td>
<td>decibel with reference to isotropic antenna</td>
</tr>
<tr>
<td>dBm</td>
<td>decibel with reference to milli-watt</td>
</tr>
<tr>
<td>(\varepsilon)</td>
<td>permittivity</td>
</tr>
<tr>
<td>(\varepsilon_r)</td>
<td>relative permittivity (dielectric constant)</td>
</tr>
<tr>
<td>(\varepsilon_0)</td>
<td>permittivity of free space</td>
</tr>
<tr>
<td>3D</td>
<td>three dimensional</td>
</tr>
<tr>
<td>ADS</td>
<td>advance design system</td>
</tr>
<tr>
<td>(B_s)</td>
<td>saturation flux density</td>
</tr>
<tr>
<td>(B_r)</td>
<td>remanence flux density</td>
</tr>
<tr>
<td>BEOL</td>
<td>back end of line</td>
</tr>
<tr>
<td>C</td>
<td>capacitor</td>
</tr>
<tr>
<td>CPS</td>
<td>coplanar strips</td>
</tr>
<tr>
<td>CPW</td>
<td>coplanar wave-guide</td>
</tr>
<tr>
<td>(C_{ox})</td>
<td>oxide capacitance</td>
</tr>
<tr>
<td>(C_{ox})</td>
<td>substrate capacitance</td>
</tr>
<tr>
<td>D</td>
<td>distance</td>
</tr>
<tr>
<td>DRA</td>
<td>dielectric resonator antenna</td>
</tr>
<tr>
<td>CBPA</td>
<td>cavity backed patch antenna</td>
</tr>
<tr>
<td>CAD</td>
<td>computer aided design</td>
</tr>
<tr>
<td>CMC</td>
<td>Canadian microelectronics corporation</td>
</tr>
<tr>
<td>CMOS</td>
<td>complementary metal oxide semiconductor</td>
</tr>
<tr>
<td>DRC</td>
<td>design rule check</td>
</tr>
<tr>
<td>E</td>
<td>electric field</td>
</tr>
<tr>
<td>EM</td>
<td>electromagnetic</td>
</tr>
<tr>
<td>ESD</td>
<td>electrostatic discharge</td>
</tr>
<tr>
<td>EuWIT</td>
<td>european wireless technology conference</td>
</tr>
<tr>
<td>G</td>
<td>gain</td>
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<tr>
<td>(G_p)</td>
<td>gain of patch antenna</td>
</tr>
<tr>
<td>Symbol</td>
<td>Definition</td>
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<tr>
<td>--------</td>
<td>-----------------------------------------------------</td>
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<tr>
<td>Gc</td>
<td>gain of on-chip antenna</td>
</tr>
<tr>
<td>GHz</td>
<td>gega hertz</td>
</tr>
<tr>
<td>GPS</td>
<td>global positioning system</td>
</tr>
<tr>
<td>GSG</td>
<td>ground signal ground</td>
</tr>
<tr>
<td>gm</td>
<td>transconductance</td>
</tr>
<tr>
<td>HFSS</td>
<td>high frequency structural simulator</td>
</tr>
<tr>
<td>Hc</td>
<td>coercivity</td>
</tr>
<tr>
<td>I</td>
<td>current</td>
</tr>
<tr>
<td>IC</td>
<td>integrated circuit</td>
</tr>
<tr>
<td>J</td>
<td>current density</td>
</tr>
<tr>
<td>K</td>
<td>Boltzman constant</td>
</tr>
<tr>
<td>T</td>
<td>tesla</td>
</tr>
<tr>
<td>l_s</td>
<td>slot length</td>
</tr>
<tr>
<td>Ls</td>
<td>series inductance</td>
</tr>
<tr>
<td>LCP</td>
<td>liquid crystal polymer</td>
</tr>
<tr>
<td>LTCC</td>
<td>low temperature co-fired ceramic</td>
</tr>
<tr>
<td>M</td>
<td>magnetic field</td>
</tr>
<tr>
<td>MCM</td>
<td>multichip module</td>
</tr>
<tr>
<td>MHz</td>
<td>mega hertz</td>
</tr>
<tr>
<td>MIM</td>
<td>metal insulator metal</td>
</tr>
<tr>
<td>Ms</td>
<td>saturation magnetization</td>
</tr>
<tr>
<td>NF</td>
<td>noise figure</td>
</tr>
<tr>
<td>NMOS</td>
<td>n-type metal oxide semiconductor</td>
</tr>
<tr>
<td>Oe</td>
<td>Oersteds</td>
</tr>
<tr>
<td>P</td>
<td>power</td>
</tr>
<tr>
<td>PCB</td>
<td>printed circuit board</td>
</tr>
<tr>
<td>PLL</td>
<td>phase lock loop</td>
</tr>
<tr>
<td>PMOS</td>
<td>p-type metal oxide semiconductor</td>
</tr>
<tr>
<td>PTFE</td>
<td>polytetraflourethylene</td>
</tr>
<tr>
<td>Pt</td>
<td>transmitted power</td>
</tr>
<tr>
<td>Pr</td>
<td>received power</td>
</tr>
<tr>
<td>Pr_p</td>
<td>received power from ptch antenna</td>
</tr>
<tr>
<td>Pr_c</td>
<td>received power from on-chip antenna</td>
</tr>
<tr>
<td>Q</td>
<td>quality factor</td>
</tr>
<tr>
<td>R</td>
<td>distance between receive and transmit antennas</td>
</tr>
<tr>
<td>RF</td>
<td>radio frequency</td>
</tr>
<tr>
<td>RFIC</td>
<td>radio frequency integrated circuit</td>
</tr>
<tr>
<td>RFID</td>
<td>radio frequency identification</td>
</tr>
<tr>
<td>RADFET</td>
<td>Radiation Field effect Transistor</td>
</tr>
<tr>
<td>R_s</td>
<td>series resistance</td>
</tr>
<tr>
<td>R_sub</td>
<td>substrate resistance</td>
</tr>
<tr>
<td>RXC</td>
<td>rectangular waveguide cavity</td>
</tr>
<tr>
<td>RX</td>
<td>Receiver</td>
</tr>
</tbody>
</table>
S  surface
Si  silicon
S_{21}  transmission gain
S_{11}  input return loss
SiP  system-in-package
SoC  system-on-chip
SoP  system-on-package
SOI  silicon on insulator
TE  transverse electric
TX  transmitter
Tan\delta  loss tangent
LNA  low noise amplifier
U-NII  unlicensed national information infrastructure
\mu  permeability
\mu_0  permeability of free space
\mu_{lin}  Linear permeability
\mu_r  relative permeability
V  volume
V_{DD}  drain voltage
VCO  voltage-controlled oscillators
V_h  horizontal voltage
V_v  vertical voltage
WLAN  wireless local area networks
W_s  slot width
Z_L  load impedance
Z_{in}  input impedance
Z_r  receive antenna impedance
Z_s  source impedance
Z_{ant}  antenna impedance
Z_0  characteristic impedance
Chapter 1

1 Introduction

Low cost wireless sensor systems are becoming crucial in modern day health care. These can be utilized in a number of applications like continuous monitoring of human vital signs, remote health care, locating patients in a hospital environment, communicating the dose of automated medicine to medical staff and measuring radiation dose in radiotherapy applications. The wireless aspect is not only revolutionary for health care delivery but also brings in added convenience for the patients. The desired characteristics for such a wireless device are very small size, minimum power consumption and low cost. The miniaturization and low cost requirements can be achieved by employing low cost CMOS integrated circuit (IC) technology in a System-on-Chip (SoC) format with a minimum number of off-chip components. For added flexibility, functionality and efficiency, a System-on-Package (SoP) approach can be followed as an alternate solution for such wireless biomedical sensor systems. In this regard, Low Temperature Co-fired Ceramics (LTCC) technology offers many attractive features and possibilities. Size reduction is possible because of the 3D nature of the multi-layer, low loss
medium and because passive components such as capacitors, resistors, inductors and antennas can be embedded, allowing for a high degree of integration.

1.1 Motivation

A miniature SoC or SoP would be an ideal solution for many short-range wireless sensor applications. For example, in the treatment of cancer patients by means of high energy radiation, precise knowledge of the dose and location of radiation experienced by the body is essential. Typically this measurement is made by a wired sensor to record the high energy radiation dose as shown in Figure 1.1 [1]. These radiation sensors are small enough to be placed on any part of the body during a radiotherapy session, helping doctors to appropriately treat malignant tumors by providing real-time data on the radiation doses reaching the organs. These radiation measurement systems are called dosimeters, and while they have good sensitivity, the required wiring harness (shown in Figure 1.2) is large and can deflect or scatter radiation away from the targeted region during the irradiation process. To avoid these ill effects and to relieve patients from a cluster of wires on their bodies, a short range radio for transmitting the sensor data would be preferred. A similar application is the Extra Vehicular Activity Radiation Monitoring (EVARM) project which is designed to measure radiation doses absorbed by astronauts in extra vehicular activity i.e., spacewalks [2]. The uncertainty of the space radiation environment can lead to significant risks to both humans and electronics. Existing systems do not allow real time continuous monitoring of the radiation experienced by the astronauts and the electronics.
1.2 Challenges

Over the last few years researchers have been striving to find a reliable solution for a wearable wireless biomedical sensor system; however a compact, dependable and low cost wireless device is still a farfetched dream. Furthermore, a non-invasive, wearable, low power, continuous monitoring and miniaturized wireless dosimeter is still in the research phase and far
from commercialization. The major challenges associated with the development of such a system are designing accurate non-invasive sensors, realizing low power transmitter (TX) and receiver (RX) circuits with miniature integrated antennas, designing on-chip interface signal processing circuitry between the sensors and the TX circuit, incorporating a very small battery that is transparent to high energy radiation and, of prime importance, integrating all of the above components on a small, and low cost platform. Details of the specific challenges related to this work are given below.

**Miniature Integrated Antenna**

In order to keep the TX size to a minimum, the antenna (which is the largest part of a typical TX module) has to be miniaturized. Figure 1.3 shows that the major portion of a modern handheld wireless device like the *iphone* is occupied by the antenna and the battery [3]. If the antenna can be integrated with circuits on the chip, a very low cost and compact system could result, as shown in Figure 1.4 [4]. However standard CMOS silicon substrate is a very lossy medium for antenna realization, which results in in-efficient antennas. Furthermore, it is extremely difficult to fit these antennas on-chip, as they are generally a significant fraction of a wavelength in size. This becomes increasingly challenging for lower frequency bands. The presence of on-chip circuitry and other metals in close vicinity of the antenna makes the design even more complicated. Experimental characterization of such small on-chip antennas requires custom jigs and innovative techniques [5]. In addition, the realization of miniature antennas within a package presents a number of antenna package co-design challenges.
Packaging

All ICs are housed in a package before they can be placed on a board. These packages are much greater in size than the bare die and hence cause unnecessary enlargement of the module. Sometimes multiple chips are packaged together in a horizontal fashion to act as a single functional block. This packaging technique is called Multi-Chip-Module (MCM). Miniaturization requirements forced the electronics industry to 3D packaging or vertical integration of these chips, typically known as System-in-Package (SiP). However neither of the
above approaches addresses the bulk of the components in any electronic system, passive components and interconnections. Greater integration and functionality can be achieved if passives like inductors, capacitors, filters, couplers and antennas are realized within the package itself. Modern packaging materials like LTCC and Liquid Crystal Polymer (LCP) enable designers to achieve this goal, thus paving the way to a new generation of packaging now known as SoP as shown in Figure 1.5[6]. The combination of multiple technologies in a single 3D system shown in Figure 1.5 is still in the research phase and far from being employed as a commercial device. Here the major design challenge is the requirement for IC, circuit and package co-design. Large volume production and fabrication tolerances are also an issue with these modules.

Figure 1.5 3D integration concept in SoP module [6]
1.3 Research Objectives

This work is part of a collaborative project regarding a wireless dosimeter design with a fellow PhD student Muhammad Arsalan. The concept of the wireless dosimeter is shown in Figure 1.6. Two design approaches have been shown, namely, SoC and SoP.

This thesis focuses on the design and development of a TX chip with an on-chip antenna for the SoC approach. For the SoP, it will deal with the LTCC package design with integrated antenna suitable for the wireless dosimeter application. It investigates the design aspects of different components required to realize efficient SoC and SoP solutions. It also compares the performance of the two approaches. Finally, it investigates novel packaging techniques and materials to not only lower the power consumption and cost of the system, but also to make it tunable and reconfigurable. Specifically, the following are the objectives for operation in the Unlicensed National Information Infrastructure (U-NII) 5 GHz radio band [7].

a) Design a miniaturized on-chip antenna suitable for integration with a standard CMOS technology based TX circuit.

b) Design a standard CMOS technology based TX chip which makes use of the on-chip antenna for a SoC demonstration of short range communication. It must have the capability to function with an off-chip antenna for a SoP demonstration having an extended communication range.

c) Design an on-chip antenna for integration with a standard CMOS technology based RX circuit.
d) Design an LTCC package with an efficient antenna for the SoP demonstration.

e) Investigate novel packaging techniques for reduced part count and improved efficiency.

f) Develop an analytical model to support the novel SoP design in (e).

g) Investigate novel LTCC packaging materials such as ferrite ceramics to achieve tunablity and reconfigurability.

---

**Figure 1.6 Wireless dosimeter (a) SoC block diagram (b) SoP block diagram**

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1.4 Thesis Contributions

The major contributions of this work are listed below:

Contribution # 1: Oscillator TX with On-chip Inductor/Antenna

The smallest reported oscillator TX and on-chip antenna design for 5 GHz band has been demonstrated. The design is unique because the on-chip antenna performs double duty as an inductor in the resonant tank of the oscillator transmitter.

Contribution # 2: LTCC SoP Design

An advanced packaging technique has been developed which connects the transceiver circuits of a silicon chip to an embedded package antenna in a completely novel way. This new design eliminates the requirement of additional components such as buffer amplifiers, matching circuits and interconnects lines.

Contribution # 3: Novel LTCC SoP Analytical Model

A simple analytical model has been developed to support the new aperture coupled LTCC SoP module. It provides insight into the designable parameters of the SoP. In particular, it allows the determination of the optimum position for the TX chip in the package.

Contribution # 4: Ferrite LTCC Material Characterization

Magnetostatic and microwave characterization of the ferrite LTCC tape system ESL 40012 [8] is performed in this thesis, employing novel solenoid and toroid transformers that are completely embedded in the LTCC material under test. This is the first demonstration of
completely embedded toroid transformers in ferrite LTCC, showing better performance as compared to the solenoids. For the first time, material parameters ($\varepsilon_r$, $\tan\delta$, $M_s$ etc) needed for the design of tunable SoPs have been accurately determined.

**Contribution # 5: Ferrite LTCC Based Antennas for Tunable SoP**

Novel tunable antennas are designed in a ferrite LTCC medium. These antennas operate in the ferrite's partially-biased state and are frequency tuned by the magnetostatic field produced in a winding that, for the first time, is completely embedded in the ferrite LTCC substrate.

**Publications and Patent**

Two journal papers [9][10] and ten conference publications [11-20] have already been published. One more journal paper has been accepted for publication [23]. Two more journal papers have been submitted recently [21-22]. A pending US patent has also resulted from this work [24].

**Statement of original Contributions in Joint Publications**

Some parts of this thesis were done in collaboration with other students. The details of the collaborative work and the resultant publications are listed below.

The phase lock loop transmitter chip was done in collaboration with Victor Karam and Peter Popplewell. The author was responsible for on-chip antenna design and measurement aspects. One journal [9] and four conference publications resulted from this collaboration.
The receiver chip was done in collaboration with Muhammad Arsalan. Again the author was responsible for the on-chip antenna design and measurements. One journal paper [23] has been accepted for publication from this work.

Faculty members Dr. Joey Bray, Dr. Nasrin Hojjat, Dr. Calvin Plett, Dr. John Rogers and Dr. Maitham Shams have been providing assistance in an advisory role and are co-authors of some publications as well.

Significance of Work

This work is the first demonstration of a wearable wireless dosimeter which can measure the radiation dose in real time. The prototype developed in this work demonstrates the feasibility of highly miniaturized, ultra-low power, wireless biomedical sensor systems in standard low cost CMOS process. Though the design is specific to radiotherapy application, the concept can be applied to other applications like legal badges in nuclear labs, radiation monitoring for astronauts during space walks, radon gas detection and UV index monitoring.

The work in thesis has received many awards. The conference paper [19] won the ‘overall best paper prize’ in European Wireless Technology Conference (EuWiT) at European Microwave Week in Amsterdam [124]. The demonstration of conventional LTCC TX module won the national technology innovation competition during the Canadian Microelectronics Texpo [125]. The author also received the Ottawa Carleton Research Innovation (OCRI) “2008 Researcher of the year award” for this work.
1.5 Thesis Outline

There are six chapters in this thesis, organized as follows.

Chapter 1 covers the introduction to the thesis. It highlights the concept, major challenges and thesis contributions.

Chapter 2 gives a brief overview and theory for the SoC and SoP approaches. It also presents the literature review for all the major components of the RF SoP. It highlights the short comings of the existing components in comparison to the proposed ones.

Chapter 3 explains the oscillator TX with on-chip antenna design. The design strategy from Electromagnetic (EM) simulations to circuit simulations and realization is described. Some design tradeoffs and measurement challenges are described for SoC applications.

Chapter 4 describes the LTCC SoP and passives design. It demonstrates the tradeoffs between SoC and SoP designs. A novel aperture coupled LTCC SoP design is also explained in this chapter.

Chapter 5 encompasses the ferrite LTCC part. The first half of the chapter deals with the material characterization techniques and measurements. The remainder of the chapter deals with tunable antenna design. Possible short-comings are highlighted and improvements in the design are suggested.

Chapter 6 concludes the thesis with a summary of the work and some recommendations for future research.
Chapter 2

2 SoC and SoP Overview

In the past, portable electronic consumer products were discrete, meaning that they were expected to perform only one job. Telephones would only provide voice communication service and audio, video products would only provide audio and video functions. Computers were used to process data and there were individual modules for cameras and video games. However with the emergence of cell phones, in particular 3G phones like iPhone, trends have shifted from discrete systems to highly integrated systems with built in multi-functions. This is not only restricted to the cell phone industry; in fact, it has penetrated into the consumer, automotive, and biomedical industries as well. The future personal handheld (or wearable device) is expected to have features such as cell phone, camera, GPS, internet, satellite TV, advanced computing and health monitoring. One possible concept of a future device is the Nokia Morph phone, shown in Figure 2.1 [25]. This surge of highly integrated and multifunction devices has necessitated the designers to think outside the box for solutions which are unconventional. The new trends have provided the impetus for low cost and compact SoC and SoP approaches. This
chapter will deal with the background literature related to these concepts and will compare different solutions. It will focus on the various RF systems reported in the literature realized in SoC and SoP formats, with particular interest in the co-design aspects of circuits and integrated antennas. The chapter will conclude with the discussion of some novel packaging materials and techniques.

Figure 2.1 Future generation Nokia Morph phone concept [25]

2.1 System-on-Chip (SoC)

SoC integrates all components of an electronic system into a single IC (chip). It may contain analog, digital and RF functions as shown in Fig 2.2 [6]. An extension of SoC is to fabricate a complete end product with all the circuit blocks and passives (like antennas and filters) built on-chip. This would be the ultimate in light weight, compact and low cost system design for mass production. The major advantages of SoC are miniaturization and cost reduction. Lower cost results from the reduction of total component count, both in terms of ICs and passives. Further cost reduction comes from lower overheads of interconnects between different ICs and discrete surface mount components. However, the realization of a complete end product on a single chip is still a farfetched dream because of numerous challenges. At the system level, this
requires long design times due to complex integration requirements, which also increases the
cost per wafer as a result of the numerous mask steps involved. Intellectual property issues
become prominent when designs from the analog, digital and RF worlds are brought together
on a single chip [6]. Testing complexities and costs, performance and power dissipation are also
challenges. At the component level, a lack of upgrade flexibility of any one element
independently is a major limitation. On-chip passives are inefficient and their size at lower
frequencies is unsuitable for on-chip realization. This is especially true for on-chip antennas
[26].

2.2 System-in-Package (SiP)

System-in-Package is an extension of the Multi-Chip-Module (MCM) approach. In an MCM,
instead of integrating all functions on a single chip, several small chips are fabricated and are
interconnected on a single platform [27]. The chips are placed horizontally as shown in Figure
2.3[6]. However the emergence of cell phones necessitated 3D vertical interconnects of chips
instead of horizontal. This vertical stacking of similar or dissimilar chips in a package is referred
to as SiP as shown in Figure 2.4 [6].
In contrast to SoC, SiP has clear advantages like simpler IC designs and fabrication, faster time to market, and minimal IP issues. It miniaturizes by combining multiple ICs and discrete components into a single 3D package. It allows a system to be partitioned into separate RF/analog/digital blocks. The SiP approach to system-level integration allows designers the flexibility they require to upgrade discrete ICs and reduce cost. It can be said that SiP occupies a "sweet spot" between SoC and traditional, separately packaged parts. SiP provides the desired SoC performance benefits of lower power and higher speed in a small footprint, while avoiding the high cost of fabrication, test, and time-to-market delays [28].

Despite all the advantages of SiP over SoC, in large volumes SoC is believed to be more cost effective than SiP since the former fabrication increases the yield and because its packaging is simpler. Moreover SiP design requires advanced combinations of CAD tools, IC technology and packaging capabilities [6].

---

**Figure 2.3 MCM Concept [6]**

**Figure 2.4 SiP Concept [6]**

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2.3 System-on-Package (SoP)

All the above mentioned packaging techniques have one fundamental limitation. They have traditionally depended primarily on CMOS ICs for the system characteristics, and the packaging is used for mere interconnects. Though SiP can embed both active and passive components, it can only accommodate bulky thick film passive components. SoP goes one step farther by integrating thin film passive components on the package substrate. In typical consumer electronics systems, such as cell phones, only 10% of the system components are made up of ICs [27]. The remaining 90% are passive components, boards, and interconnections. This so-called "90% of the system problem" is being addressed by systems-on-package (SoP). SoP transforms millimeter-scale discrete components into micrometer or nanometer-scale embedded thin-film components, thus reducing system size by up to a million times [27].

RF components like capacitors, filters, high Q inductors and antennas are realized within the package in an efficient way. This added functionality in the package ensures that it is not only a medium for interconnects; rather, it is the system itself as shown in Figure 2.5 [6]. The SoP approach is very useful for future highly integrated, multi-technology, multi-function systems like bioelectronics Radio Frequency Identification (RFID) tags or hand held personal communication devices. It can not only embed RF passives but can accommodate high speed optical interconnects and waveguides. Another major advantage of SoP is that it can have micro-scale interconnects which can reduce the delay caused by the extra resistance of nano-scale interconnects in SoC. In short, the SoP concept integrates multiple system functions into a single, compact, low cost and high performance packaged system.
2.4 RF SoC Overview

The performance improvement in advanced CMOS technology has paved the way to RF component integration with analog and digital circuitry on a single chip [29-31]. These scaled-down CMOS devices exhibit high cut-off frequencies, high performance integrated passives and operate at lower voltages. This progress of RF CMOS SoC has enabled highly compact handheld and portable devices. The attractiveness of these systems is that they can offer low cost, small physical size and low power consumption. This concept has been widely accepted in applications like Wireless LAN and Bluetooth and is making inroads to cellular transceivers and GPS receivers [32]. It has also found its utility in many modern wireless sensor networks [33].

Though substrate noise coupling and low Q passives in standard low resistivity bulk silicon are still a challenge for efficient SoC implementation, a few completely integrated components and transceiver systems have nonetheless been successfully demonstrated [34]. Even these are not perfect SoC embodiments due to their requirement for off-chip components or non-standard IC processes. A Bluetooth CMOS based transceiver SoC is shown in Figure 2.6 [35]. However, this SoC leaves the reference crystal and antenna off-chip. Recently, a 77 GHz phased array transceiver with on-chip antennas has been demonstrated [36]. However in order to
achieve acceptable antenna efficiency many additional fabrication steps were performed. In another example of an RF SoC, a 24 GHz receiver with an on-chip antenna was demonstrated, but on a high resistivity SiGe platform [37].

![CMOS Transceiver SoC architecture](image)

Figure 2.6 CMOS Transceiver SoC architecture [35]

Part of this thesis deals with an RF transmitter having an integrated antenna in SoC format. Accordingly, the following sections will highlight some of the previous work done on oscillator IC TX’s and IC antennas. Very little prior work exists on monolithic designs that combine both parts. Section 2.4.1 discusses some relevant examples of oscillator transmitters, whereas on-chip antennas are discussed in section 2.4.2.

### 2.4.1 Oscillator Transmitter

The function of the TX is to transmit a low frequency signal on a RF carrier via an antenna. For the wireless transmission of medical sensor data, the TX design considerations are small size, low power, low data rate and short range. An oscillator TX is the simplest architecture, which generally consists of just an oscillator. The control line of the oscillator can directly be
modulated in this scheme. In terms of performance parameters like low power consumption and efficiency, the oscillator TX is one of the leading architectures [38]. The major drawbacks are that the design is susceptible to temperature and environment variations because it is not locked to a reference frequency. In [39], a fully differential LC tank based oscillator transmitter has been demonstrated for neural recording applications at 433 MHz. This design employs an off-chip monopole antenna and can communicate over only 1 m of range. Oscillator transmitters are generally intended for short range communication, so, a power amplifier is not required and the oscillator drives the antenna directly. In some examples of oscillator TX for wireless sensor networks, however, very low power amplifiers are also employed [40][41]. None of these transmitters employ an on-chip antenna. An interesting example of a low power oscillator TX utilizes the inductor of the resonant tank of the oscillator as the radiating element [42]. This work has been done for 400 MHz biotelemetry application. However, it does not qualify as a true monolithic design as it combines an off the shelf transistor with a non-standard silicon process. Despite micromachining efforts to reduce the loss of the inductor, it can only communicate over a distance of 0.9 m.

2.4.2 On-chip antenna

This section will discuss on-chip antennas, with the last part dedicated to the inductive on-chip antennas.

An on-chip antenna represents a possible solution for a fully integrated wireless system with no off-chip components. Antenna impedance can be utilized to replace the matching network interfacing between antenna and the RF front-end circuitries. The replacement not
only reduces cost but also improves circuit performance because bond pads and bond wires are eliminated. The field of on-chip antennas is still quite young, but it is growing at a fast pace. Many monolithic Si integrated antennas have previously been demonstrated, with some of them summarized in Table 2.1. The on-chip antenna design in literature is mostly restricted to higher frequencies like 10 GHz and above due to large size of antennas at lower frequencies. On-chip antennas, as described in the literature, are either utilized to provide inter and intra-chip wireless interconnects [43-46] or for short range air transmission [47-53]. The former antennas display high transmission loss and are not characterized for element gain and radiation pattern whereas the latter often utilize additional processing steps to increase the resistivity of Si substrates in an attempt to enhance the antenna performance. These additional wafer processing steps like proton implantation and Back End of Line (BEOL) add to the processing cost of Si wafers. However, the major challenge is the poor radiation efficiency due to lossy Si substrate. Also, realizing on-chip antennas for lower microwave frequencies is a challenge. Additional problems are faced during the experimental characterization of such miniature antennas [54].

Recently an attempt has been made to improve the radiation efficiency and gain of on-chip antennas but an un-doped silicon substrate is used under a standard wafer [36]. Moreover many post processing steps are performed to incorporate matching layer and a large silicon lens on the backside of the chip to enhance the antenna gain from -8 dBi to 2 dBi. Similarly in [37], a high resistivity SiGe platform is used to enhance the antenna gain to -2 dBi. The 24 GHz Rx chip with on-chip antenna is shown in Figure 2.7.
Table 2.1 Antenna Comparisons with Previously Published Work

<table>
<thead>
<tr>
<th>Ref</th>
<th>Application</th>
<th>Antenna Type</th>
<th>Size L x W</th>
<th>Substrate Material</th>
<th>Gain</th>
<th>Comments</th>
</tr>
</thead>
<tbody>
<tr>
<td>[43]</td>
<td>Wireless Interconnect *</td>
<td>Dipole</td>
<td>2mm x 10um</td>
<td>Si 10Ω-cm</td>
<td>-56dB@18GHz*</td>
<td>High transmission loss</td>
</tr>
<tr>
<td>[44]</td>
<td>Wireless Interconnect</td>
<td>Dipole</td>
<td>2mm x 1um</td>
<td>Si 5Ω-cm</td>
<td>-65dB@18GHz</td>
<td>High transmission loss</td>
</tr>
<tr>
<td>[45]</td>
<td>Wireless Interconnect</td>
<td>Dipole</td>
<td>2mm x 10um</td>
<td>Si 10Ω-cm</td>
<td>-36.5dB@18GHz</td>
<td>Additional Si processing steps, high loss</td>
</tr>
<tr>
<td>[46]</td>
<td>Wireless Interconnect</td>
<td>Dipole</td>
<td>2mm</td>
<td>Si 20Ω-cm</td>
<td>-45dB@24GHz</td>
<td>High transmission loss</td>
</tr>
<tr>
<td>[47]</td>
<td>Air Transmission</td>
<td>PIFA</td>
<td>10mm x 5mm</td>
<td>Si 10Ω-cm</td>
<td>Not characterized</td>
<td>Substrate too lossy to measure</td>
</tr>
<tr>
<td>[48]</td>
<td>Air Transmission</td>
<td>Monopole</td>
<td>900um x 920um</td>
<td>Si 10Ω-cm</td>
<td>-6dBi@40GHz**</td>
<td>Single-ended antenna, non-uniform radiation pattern, high frequency</td>
</tr>
<tr>
<td></td>
<td>Air Transmission</td>
<td>Monopole</td>
<td>900um x 920um</td>
<td>Si 10Ω-cm</td>
<td>3dBi@40GHz**</td>
<td></td>
</tr>
<tr>
<td>[49]</td>
<td>Air Transmission</td>
<td>Dipole</td>
<td>620um x 380um</td>
<td>Si (hi-res)</td>
<td><a href="mailto:0.9dBi@76.5GHz">0.9dBi@76.5GHz</a> **</td>
<td>Additional Si processing steps, high frequency</td>
</tr>
<tr>
<td>[50]</td>
<td>Air Transmission</td>
<td>Folded patch</td>
<td>3mm x 3mm</td>
<td>Si 10Ω-cm</td>
<td>Not characterized</td>
<td>Additional Si processing steps, large size</td>
</tr>
<tr>
<td>[51]</td>
<td>Air Transmission</td>
<td>Zigzag antennas</td>
<td>3mm x 0.03 mm</td>
<td>Si 20Ω-cm</td>
<td>-70 dB@24GHz</td>
<td>High transmission loss at a range of 0.1m.</td>
</tr>
<tr>
<td>[52]</td>
<td>Air Transmission</td>
<td>Inverted-F</td>
<td>2mm x 0.01mm</td>
<td>Si 10Ω-cm</td>
<td>-19dB@61GHz</td>
<td>Additional Si processing steps, high frequency, no radiation pattern measurement</td>
</tr>
<tr>
<td></td>
<td>Quasi-Yagi</td>
<td>1.2mm x 0.01mm</td>
<td>Si 10Ω-cm</td>
<td>-12.5dB@65GHz</td>
<td></td>
<td></td>
</tr>
<tr>
<td>[36]</td>
<td>Air Transmission</td>
<td>Dipole</td>
<td>4um x 20um x 1150um</td>
<td>Si 10Ω-cm over un-doped Si</td>
<td>2 dBi @ 77GHz</td>
<td>High frequency, Low loss un-doped Si substrate, Si lens to improve the gain</td>
</tr>
<tr>
<td>[53]</td>
<td>Air Transmission</td>
<td>Coil</td>
<td>1mm x 0.5mm</td>
<td>Si 10Ω-cm</td>
<td>Not characterized</td>
<td>Post processing on Si, short communication range</td>
</tr>
<tr>
<td>[5]</td>
<td>Air Transmission</td>
<td>Conductor Backed Dipole</td>
<td>3mm x 0.5mm</td>
<td>Si 10Ω-cm</td>
<td>-8dB@24GHz</td>
<td>Differential, low cost Si, reasonable gain and good radiation pattern</td>
</tr>
<tr>
<td>[37]</td>
<td>Air Transmission</td>
<td>Folded dipole</td>
<td>3.6 mm x 0.18 mm</td>
<td>SiGe 1000 Ω-cm</td>
<td>-2dB@24GHz</td>
<td>Employing non-standard high resistivity substrate</td>
</tr>
</tbody>
</table>

* for wireless interconnect, the gain is measured as transmission gain in dB (instead of dBi), and **gain improves as frequency increases for a given antenna size
It is interesting to consider a design in which the antenna acts as an on-chip inductor and provides the required inductance and quality factor for the RF circuit it drives. This approach relies on inductive coupling between a TX and a RX, and has been reported in [55]. Though this antenna/inductor concept is economical in space and well suited for applications like RFID tags and biomedical sensor systems [56], it has traditionally been limited to very short range RF telemetry for biomedical applications [42][57][58]. In previous demonstrations, small inductors are just used as coils for near-field coupling and not optimized or characterized for their radiation properties. For example in [53], an inductor communicates over only 1 mm with a larger input power as it has not been optimized as an antenna. It, therefore, acts just as a near-field sensor and not an antenna in the classical sense.

In essence, most of the antennas reported in literature either suffer from large physical dimensions, digital CMOS incompatible material, non-standard processing or high transmission
loss resulting in limited transmission range. Recent proliferation of on-chip antennas have not been properly characterized, in particular, for their radiation pattern. When this work was started, there was no demonstration of a functional, well characterized, on-chip antenna in standard CMOS process for 5GHz band. Four years later, there is only one reported design [59], which has been published recently. It will be discussed in detail in chapter 3.

2.5 RF SoP

Though SoC offers advantages like miniaturization and lower cost, there still remain many obstacles to the actual implementation of an efficient and complete RF system on a single chip. Components like antennas, reference crystals, high Q inductors, filters, couplers and duplexers are better realized as off-chip components. Moreover, it is challenging to integrate the battery or a power source on a miniaturized chip. Practically, SoP has better potential to integrate all these components efficiently on a single platform while still maintaining very small form factors, as is shown in Figure 2.8 [60]. This concept enables the package, and not the traditional bulky board, to be the system. A SoP provides all the system functions in one single module, where all these individual components are embedded in the package instead of a typical assembly of discrete components connected together. Components can be realized on the package through a thin film implementation in mediums like LTCC and LCP [61][62][63]. On one hand such SoP components not only reduce the overall cost by eliminating the discrete components and on the other hand they can exhibit better performance than their on-chip counterparts.
Various RF SoP implementations have been reported [60, 64, 65]. Most of the SoP designs have employed LTCC substrate; however examples of RF SoP in other mediums like LCP have also been reported [66]. Three dimensional high Q embedded passives have been successfully demonstrated for SoP applications [67][68]. Initially, individual RF components like power amplifiers utilized package embedded passives to improve the performance [69][70]. Lately, an LTCC based TX module has been reported which make use of a low loss band pass filter [71]. Recently, a passive LTCC based RF front end solution has been presented for V-band, which shows an antenna and a bandpass filter integration [72]. Complete RF SoP design which employs embedded passives combined with RF circuits is demonstrated in [73].

Despite all the advancements in the SoP concept, some performance limitations still remain due to parasitic coupling and thermal management of these modules. LTCC based SoP also suffers from slightly higher fabrication tolerances, especially when it comes to the fired layer thickness. At the design automation level, modern CAD tools still lack the system level
computational ability which can handle electromagnetic and circuit simulation on a single platform. This makes the simulation of SoP, which requires mixed signal circuits, passive components and package co-design, quite challenging.

Since this thesis focuses on LTCC SoP design, the following sections present this particular SoP technology in detail.

2.5.1 Low Temperature Co-fired Ceramic

LTCC is a multilayer ceramic medium, generally used for RF and microwave packaging. It provides many advantages as compared to the typically used organic substrates like FR4, the most important being the low losses at higher frequencies. Though there are printed circuit boards (PCB) which can be multilayer and capable of high frequency operation, they are typically made of polytetrafluorethylene (PTFE), glass or ceramic which is more expensive than FR4. LTCC substrates are more suitable for multilayer circuits as compared to PCB and PTFE due to their reliability and provide higher degrees of integration with buried passives, as shown in Fig 2.9 [74]. LTCC modules are rugged and offer better thermal conductivity. Moreover the high volume production costs of small modules can be very low. An LTCC foundry can provide better yield because each layer can be manufactured and inspected in parallel before being stacked for lamination.
2.5.2 LTCC Antenna

One of the prime reasons to develop RF SoP is the possibility of realizing an integrated antenna on the package. Having an antenna on the package not only reduces the overall size of the module but also reduces the feeder losses. However, initial LTCC based RF SoP modules did not benefit from an integrated antenna [67][71][75]. This concept is challenging for lower microwave frequencies since the required antenna size may be too large to fit onto the package. Moreover very compact modules can suffer from RF circuit-antenna interference.

![3D integration of buried passives in LTCC medium](image)

Figure 2.9 3D integration of buried passives in LTCC medium [74]

Over the years, many researchers have highlighted the significance of an integrated LTCC antenna on the package [68, 76-84]. In [85], a stacked patch antenna design is presented which
exploits the multilayer LTCC medium. In order to realize efficient LTCC antennas at 76.5 GHz, [86] proposes material modulation which enables designers to optimize the antenna radiation performance. Most of the published literature revolved either around LTCC antenna design or antenna/package co-design, but the circuit/antenna co-design aspect was missing. Not until recently has the circuit, antenna and package co-design been demonstrated [72, 87, 88]. A 5 GHz Cavity Backed Patch Antenna (CBPA) has been proposed in [60] which discuss the issues related to this co-design approach. Nonetheless, still the issues related to bare die placement in cavities and interference between circuit and antenna in LTCC medium have not been rigorously investigated. Perhaps the SoP design which most closely considers these issues is shown in Figure 2.10 [73]. It shows how a shielding layer between the two vertically stacked layers of RF circuits and antenna can resolve the interference problem.

![Figure 2.10 RF circuit integration with antenna in SOP format [73]](image)

**Figure 2.10 RF circuit integration with antenna in SOP format [73]**
2.6 Ferrite LTCC Based Tunable RF SoP

Traditionally RF systems have been tuned or reconfigured through or by Microelectromechanical systems (bridges, membranes, etc) or electronic control (varactors, PIN, etc). Ferrite based RF components are, however, inherently tunable by control of their magnetic bias. In the past, such circuits have relied on large external magnets which make the system bulky and incompatible with the compact SoP concept. LTCC based RF SoP is a relatively new concept and the introduction of ferrite into the LTCC material system is still in the experimental phase. Ferrite LTCC package changes its material properties with magnetic bias and can contain embedded bias windings so that external magnets are not required. This concept was demonstrated for the first time in [89]. However, many challenges still exist which need to be resolved before the realization of a compact and efficient tunable RF SoP in ferrite LTCC.

Since part of this thesis presents ferrite LTCC based tunable antennas, the following section will discuss some ferrite based relevant antenna designs.

2.6.1 Ferrite Based Tunable antennas

Although antennas printed on ferrite substrates have been previously documented, they have relied on traditional ferrite substrates that are inherently difficult to magnetize. Unbiased ferrite substrates have been investigated as a means of reducing the size of antennas owing to the high permittivity of the ferrite medium [90, 91]. Frequency tuning of antennas has been accomplished by biasing the ferrite substrate in the low GHz frequency range [92-96]. Pattern and polarization control of ferrite-based antennas have also been successfully achieved over 5-
8 GHz frequency range [97, 98]. Most of these designs assumed uniform bias across the ferrite substrate. In [99], non-uniform biasing conditions for patch antennas on ferromagnetic substrates have been investigated. Recently, the concept of tunability has been applied to a ferrite microstrip array antenna, which can function at discrete bias points [100]. However, most of these antennas are tuned to operate in the magnetically saturated state [97]. Given that they are fabricated on traditional ferrite substrates, large external magnets (permanent or electro-magnets) must be used to provide the high magnetostatic fields. Such magnets are bulky and impractical given that 1) the substrates must operate in saturation and 2) the external fields are commensurate with the demagnetization factors of the substrates. This has typically required an external magnetic field intensity $H$ on the order of 80 000 A/m (1000 Oe).

In summary, no work has been done on tunable LTCC ferrite antennas, which makes this topic suitable for the present thesis.

2.7 Summary

SoC and SoP solutions have their own benefits and drawbacks. However, SoP appears to be a more viable solution for wireless biomedical sensor applications since it can accommodate the off-chip components in a compact 3D module. Both SoC and SoP designs presently have numerous challenges and there is great potential for improvement and innovation. For the SoC approach, on-chip antenna design and its experimental verification are some of those challenges. Similarly, antenna/circuit/package co-design has numerous unresolved issues. Ferrite LTCC based RF SoP can open a completely new era of tunable and reconfigurable devices provided several problems related to the biasing are resolved.
Chapter 3

3 SoC Design

The ever growing requirement for miniature and compact wireless devices can be met by SoC solutions. The SoC concept is beneficial for short range applications like RFID tags and wireless medical sensor systems. The attractiveness of SoC is that it can offer low cost, small physical size and low power consumption. An on-chip antenna enables designers to realize highly integrated and cost efficient systems. In accordance with the first three thesis objectives, this chapter presents the design of an RF oscillator TX, which makes use of an on-chip antenna. The design is extremely miniaturized and low power, and suitable for short range wireless dosimeter application. In addition, a new on-chip antenna design is presented for a RX SoC.

3.1 On-chip Inductor /Antenna

The oscillator TX presented in this chapter includes an on-chip antenna which is inductive and serves double duty as the inductor in the Voltage-controlled oscillator (VCO) tank. Inductive antennas have been presented previously; and these antennas were seen to either suffer from large physical size and low communication range or rely on a high resistivity substrate to
compensate for the low antenna gain and large losses of silicon [55, 57, 58, 101]. Furthermore, none of these inductor antennas were well characterized. In [42] a MHz-range oscillator TX inductor is also used as an antenna to radiate. Unfortunately, micromachining techniques are required to fabricate the dielectrically suspended loop inductor in a hybrid technology based VCO. A similar hybrid oscillator TX is presented in [56] which makes use of a large inductive antenna with short transmission range. Overall, previous on-chip inductor/antenna work has been limited to lower frequency, near field coils which have been neither designed nor characterized as antennas.

3.1.1 Novel on-chip inductor/antenna design

The design procedure adopted in this work is as follows. Since the antenna serves as an inductor for the transmitter VCO, full 3-D electromagnetic simulations using Ansoft HFSS™ are employed to obtain the required inductance “L” and quality factor “Q” while optimizing the radiation efficiency. A lumped element model is then derived for the antenna/inductor. This model allows circuit simulation of the complete antenna/TX combination using tools such as Agilent ADS™ and Cadence™.

In order for the antenna to also serve as an inductor, it must be able to retain power at the same time as it radiates power. The design is therefore required to yield a reasonably high-Q inductor as well as an appropriate antenna radiation pattern and efficiency. The loop antenna is a natural candidate for an antenna/inductor design as it is inherently inductive in nature and exhibits a broad radiation pattern. Moreover, since the loop is a differential antenna, it can be integrated with differential CMOS circuitry directly without needing a balun. Finally, its
geometry allows placement of the active TX and RX circuitry in the center of the loop, thus minimizing the die size.

The antenna is designed and implemented in IBM's standard 0.13 μm CMOS process, having a Si substrate resistivity of 13.5 Ω-cm. The metals stack up (not to scale) and loop antenna geometry are shown in Figure 3.1. In [5], the on-chip antenna is placed on top of the Si substrate and insulating oxide layer. This way the antenna is not embedded in oxide and is exposed to the air directly. However, the modern Si based CMOS processes do not allow a metal layer on top of the insulating oxide and all the metal layers are embedded in the insulating silicon-di-oxide (SiO2) layer as shown in Figure 3.1. Though 0.13 μm CMOS process is a six metal layer process, only three are shown here for simplicity. The top two metal layers (Aluminum and Copper) are generally used for on-chip inductor design. The bottom metal layer M1 can be used for realizing a shielding ground plane. Full details of the 0.13 μm CMOS process are available through Canadian Microelectronics Corporation (CMC). The antenna is realized on the top metal layer only. The loop antenna/inductor model simulated in HFSS is shown in Figure 3.2. Based on circuit analysis of a 5.2 GHz oscillator (to be described later), the objective is to obtain 1-2 nH inductor/antenna in less than 1 mm² chip area with a Q greater than 10 and acceptable radiation properties for the intended application.

Square and octagonal loop antenna geometries have been investigated in HFSS and their inductive and radiation characteristics compared. A square loop is not the best choice for an on-chip inductor because it has sharp 90° bends which increase the series resistance and therefore degrade the Q. Yet the sharp bends for the square loop tend to increase the radiation
resistance and consequently the gain of the antenna. The square loop displays 1 dB more antenna gain as compared to that of the octagonal loop antenna. For approximately same area, the octagonal loop antenna does exhibit a marginally better extracted inductance than the square loop antenna. The results suggest, the octagonal loop is a better choice for an on-chip inductor, but that the square loop is more suitable as an on-chip antenna/inductor because it offers 1 dB more gain with a minor loss in Q and L. It is worth mentioning here that this gain is achieved without a patterned ground plane. A ground plane on metal level M1 would improve the Q and L marginally by preventing the buildup of image currents and restraining the fields from reaching the lossy substrate, but at the same time it decreases the gain considerably due to its very close placement to the antenna. Further parametric analysis reveals that widening the metal strip increases the gain strongly and Q marginally. The inductance is not affected greatly by varying the width; however increases in the inner diameter of the loop antenna increase the inductance and Q considerably. After extensive analysis and optimization, a 1 mm x 1 mm square loop is designed in HFSS which provides an inductance of around 2 nH. However due to layout issues and limited chip space, the size was reduced to 825 x 675 µm2 rectangular loop. HFSS predicts an inductance of 1.45 nH and a Q of 17 at 5.2 GHz for the new dimensions. The 3D radiation pattern is shown in Figure 3.3. As expected from an electrically small loop antenna, the maximum radiation is along the plane of the loop. A useful parameter for evaluating the effectiveness of an antenna is the antenna efficiency (e_A), which is the ratio of radiated power to the total power dissipated by the antenna. The radiation efficiency can be calculated through (3.1), where R_r and R_l are the radiation and loss resistance of the antenna respectively.

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The simulated differential impedance of the inductor at 5.2 GHz is $Z_{in} = 2.7 + j 47 \Omega$, thus $R_r + R_L = 2.7 \Omega$. Similarly, the simulated efficiency $e_A$ is 0.08, and thus one can deduce that $R_r = 216 \text{ m} \Omega$ and $R_L = 2.48 \Omega$.

\[
e_A = \frac{R_r}{R_L + R_r}
\] (3.1)

Figure 3.1 On-chip antenna structure (a) CMOS process stack up (not to scale) (b) loop antenna geometry (defined on top Aluminum layer)

Figure 3.2 Antenna/Inductor HFSS model
3.1.2 Lumped Model

Precise equivalent lumped element modeling of on-chip inductors is critical for circuit design. At microwave frequencies, circuit design becomes considerably more difficult with the inclusion of many parasitic elements which are insignificant at lower frequencies. Using an accurate model, integrated circuit designers can reduce the overall turnaround time and design cost. Full-wave electromagnetic simulator tools can be utilized to extract the required lumped models, but at the cost of large computing times. Alternatively, measured/simulated S-parameters can be utilized to extract a lumped element model through optimization techniques. Many researchers have reported on the modeling of inductors on a silicon substrate and have established a very well known equivalent lumped model [102, 103], yet a modified lumped model topology is needed to represent a differential inductor. This modified model is shown in Figure 3.4 where $R_s$, $R_{sub}$, $C_{ox}$, $C_s$ and $L_s$ represent the series resistance, substrate resistance, oxide capacitance, substrate capacitance and the inductance associated with the on-chip inductor respectively [104]. The typical single-ended lumped model has two
separate branches connected to ground. Each branch has its own $R_{\text{sub}}$, $C_{\text{ox}}$ and $C_s$ in contrast to the differential model where the two branches are connected to each other, resulting in single $R_{\text{sub}}$, $C_{\text{ox}}$ and $C_s$ elements.

![Diagram](image)

**Figure 3.4 Differential inductor lumped model**

A strategy to extract the element values of the model is to develop an optimization technique which will match the simulated on-chip inductor S-parameters with the lumped model S-parameters for the frequency range of interest. ADS simulator is utilized for this optimization procedure. The ADS test bench is loaded with the HFSS simulated on-chip inductor S-parameter file. The lumped model is simulated from 100 MHz to 10 GHz (the same frequency range as that of the input S-parameter file from HFSS) and the optimization goal is set to achieve the minimum possible error between the two sets of S-parameters. The initial values for the series resistance and inductance are estimated from the simulated on-chip inductor input impedance, whereas the oxide capacitance value is roughly expected from the oxide dimensions. Table 3.1 shows the values of the lumped elements extracted from ADS. With these values, an acceptable match is observed between the HFSS and ADS S-parameters at 5.2 GHz, as shown in Figure 3.5. Though it is possible to import the s-parameters of the...
inductor/antenna directly into Cadence, the differential lumped model was developed as an intermediate verification step. Also, since this design only requires good matching at 5.2 GHz, the lumped model was not optimized further for a wideband match. For a wideband design, well-known techniques can be adopted to develop a lumped model which has a good match in the entire band of interest. It is worth mentioning here that the simple differential model shown here is unable to represent any common mode present in the design.

Table 3.1 Lumped element values from ADS

<table>
<thead>
<tr>
<th>Lumped Element</th>
<th>Value from ADS</th>
</tr>
</thead>
<tbody>
<tr>
<td>$R_s$</td>
<td>2.3 Ω</td>
</tr>
<tr>
<td>$L_s$</td>
<td>1.4 nH</td>
</tr>
<tr>
<td>$R_{sub}$</td>
<td>4.9 kΩ</td>
</tr>
<tr>
<td>$C_s$</td>
<td>7 fF</td>
</tr>
<tr>
<td>$C_{ox}$</td>
<td>500 fF</td>
</tr>
</tbody>
</table>

Figure 3.5 HFSS and ADS S-parameters from lumped model optimization set up
3.2 Oscillator Transmitter Implementations

The developed on-chip inductor/antenna will be implemented in two oscillator transmitter circuits presented in the following sections.

3.2.1 Phase lock loop with on-chip antenna

As an initial test vehicle for the 5 GHz on-chip antenna, a Phase Lock Loop (PLL) based oscillator TX circuit was developed in collaboration with a fellow PhD student Victor Karam, the details of which are given in [14]. The fabricated TX chip, is shown in Figure 3.6. The total size of the chip is 1.4 mm by 1.4 mm, in which 825 μm by 675 μm of area is occupied by the on-chip antenna. As mentioned in section 3.1.1, the antenna size was reduced in the layout because of the limited chip space. This reduced the inductance associated with the inductor/antenna and in turn shifted the operation frequency of the VCO to 6.3 GHz. The metal width of the antenna is 100 μm and it is fed differentially by the VCO placed in its centre. The rest of the chip is occupied by the bond pads, and PLL circuits which are placed outside the loop to avoid complicating the routing between the circuits and the bond pads. The VCO is placed in the centre of the loop through feed lines with microsurgery points. The bond pads can be removed through a laser trimming technique for normal operation of the VCO connected to the antenna. On the other hand, independent testing of inductor/antenna is possible through the bond pads after disconnecting the VCO from the other end of the antenna.
Inductor Measurements

The inductor/antenna was disconnected from the VCO using a semiconductor microsurgery technique, and probed for characterization as a passive single-ended inductor due to test equipment limitations. Figure 3.7 compares the inductor's simulated and measured single-ended $Q$ with the simulated differential $Q$. In Figure 3.8 the same comparisons are made for $L$. The measured and simulated single-ended $Q$ are in close agreement across the band of interest, which validates the simulation technique. This also confirms that the simulated results for differential $Q$ are reliable. As can be seen from Figure 3.7, the differential $Q$ value is significantly higher (as expected) and this value was employed in the TX circuit analyses. At the design frequency of 5.2 GHz, an input impedance of $Z_{in} = 9.6 + j58 \, \Omega$ was measured, corresponding to an inductance of 1.75 nH. The discrepancy between the simulated and measured inductance is

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0.3 nH, which can be attributed to extra narrow interconnects leading to the bond pads from the antenna's feeding paths. Also, the measured inductance appears to have a lower self-resonate frequency, which is probably a result of the bond pads' parasitic capacitance.

Figure 3.7 Simulated vs measured Q of inductor/antenna

Figure 3.8 Simulated versus measured inductance of inductor/antenna
Antenna Measurements

A challenging part of this work is to measure the gain and radiation pattern of the miniature antenna. In order to avoid the complexities of an external balun and the accompanying de-embedding procedure, or the use of elaborate differential test equipment, the antenna is tested while connected to the VCO. Since the antenna is fed by the TX VCO, it does not require to be connected to the signal source for testing in the usual way. Rather, the radiating chip is mounted on a printed circuit board with RF connectors and placed vertically in an anechoic chamber, with the received signal collected by a spectrum analyzer via a patch antenna. The setup is shown in Figure 3.9. The measurement setup is first calibrated using two identical microstrip patch antennas at a distance of 30 cm from each other. The TX patch antenna is connected to the signal generator whereas the RX patch antenna is connected to the spectrum analyzer. The transmit power \( P_t \) at the patch antenna must be the same as that supplied by the VCO to the on-chip antenna.

Considering that the supply voltage for this technology is 1.2 V, the differential peak voltage across the inductive antenna \( V_{\text{ANT, diff}} \) is assumed to be 1.2 V. The power delivered can then be calculated by applying this voltage across the differential real impedance of the antenna, \( R_{\text{ANT, diff}} \). According to the antenna's series resistance \( R_{\text{ANT}} = 2.7 \, \Omega \) and quality factor \( Q_{\text{ANT}} = 17 \), the differential resistance can be found with the following impedance transformation

\[
R_{\text{ANT, diff}} = R_{\text{ANT}} (Q_{\text{ANT}}^2 + 1) = 783 \, \Omega
\]

\( (3.2) \)
Thus, the power delivered to the antenna is expected to be $P_t = \frac{V_{\text{ANT, diff}}^2}{2R_{\text{ANT, diff}}} = 920 \mu W$, or approximately 0 dBm. Since the antenna’s radiation efficiency is 8%, the power radiated is $P_{\text{rad}} = 0.08 \cdot P_t = 73.5 \mu W$.

Both the patch antennas have a gain ($G_p$) of 6.7 dBi and by supplying the required power to the TX patch antenna, a received power ($P_{rp}$) of -24.8 dBm is recorded. Next, the TX patch antenna is replaced by the TX chip having the on-chip antenna. The RX patch antenna is left untouched. In this measurement setup, a received power ($P_{rc}$) of -69.8 dBm is recorded. The gain of the chip antenna ($G_c$) can now be calculated from (3.3), which is derived from the Friis transmission equation [105], knowing that the frequency, distance and transmit power remain the same as in the calibration measurement.

$$G_c = P_{rc} - P_{rp} + G_p$$  \hspace{1cm} (3.3)

![Figure 3.9 On-chip antenna radiation pattern measurement setup](image-url)
The chip antenna is next rotated in the azimuthal plane (in steps of 15°, from +90° to -90° off boresight) and the gain is plotted for every step. Note that ±90° corresponds to the plane of the loop. The resultant radiation pattern is shown in Figure 3.10. A spline interpolation method is employed to plot a smooth radiation pattern from a discrete set of data points. The peak gain lobe is slightly off from the plane of the loop; however a null is measured at boresight, as expected. The region from boresight to -90° did not produce a symmetrical pattern due to strong parasitic coupling and interference from the PLL circuits (and the large loop filter capacitors) on that side of the chip. In comparison to the simulated radiation pattern, the measured radiation pattern is more tilted towards boresight because of the asymmetrical position of the antenna with respect to the edges of the die. Additionally, the measured antenna is mounted on a printed circuit board (PCB) with a large ground plane and numerous passive components, none of which are present in the HFSS model. A maximum gain of -22 dBi is achieved. Positioning the on-chip antenna at the maximum gain angle, the RX patch antenna is then moved back in steps of 30 cm. The received power is recorded for different separation distances and the results are plotted in Figure 3.11. A close match is observed between theory and the measured results. With a transmitted power of 1.3 dBm, the on-chip antenna on the TX side can communicate with an off-chip patch antenna on the RX side placed 2 m away. The range is limited by the RX sensitivity which is -70 dBm in this case.
Gain for 15 degrees steps

- spline

Peak shifted due to

Interference from RF circuits
asymmetric loop/die
geometry

Figure 3.10 Measured radiation pattern
3.2.2 Voltage Controlled Oscillator TX with on-chip antenna

In the PLL based implementation, some of the active circuits were placed outside the loop and were very close to one of the antenna edges. This resulted in deteriorated radiation performance. Therefore a new TX chip has been designed which operates as an oscillator TX and does not require the PLL circuits and an off-chip reference crystal. This design has been completely conducted by the author, and is customized for subsequent integration with radiation sensors. The TX here makes use of direct modulation of VCO with no closed feedback loop. This method has the advantage of the data rate not being limited by the loop bandwidth of a phase lock loop circuit. Moreover, the direct modulation of a closed loop VCO would cause the modulated waveform to distort by the negative feedback loop of a PLL [106]. Above all, a PLL circuit would consume more power than a simple VCO and would require a reference
signal, which is an off-chip crystal in most cases. On the other hand, the open loop direct VCO modulation does suffer from the fact that the output frequency is susceptible to undesired perturbation and noise. For the biomedical application being pursued in this work, the absolute value of the free running VCO frequency is less important than the variation in the carrier frequency due to modulation. Moreover, dosimeter sensor data modulation would cause the free running VCO frequency to vary in only one direction permanently. Therefore any frequency drift due to temperature or jitter can be easily identified and compensated for.

**Modified On-chip Inductor/Antenna Design**

In the present design, care has been taken that the antenna remains close to the chip edges without any active circuits blocking it. The shape of the inductor/antenna is slightly altered to fit it in the available chip space of 1.5 mm$^2$ (Canadian Microelectronics chip allocation) as shown in Figure 3.12 (VCO not part of the HFSS model). For this design, HFSS model includes the bond pads, connecting lines and the microsurgery points. For the modified loop, HFSS predicts an inductance of 1.4 nH and a Q of 14 at 5.2 GHz.
Voltage Controlled Oscillator Design

An LC cross-coupled differential VCO topology has been chosen for this work, and is shown in Figure 3.13. It utilizes both PMOS and NMOS transistors, which generate negative resistance to cancel the resonant tank losses. The resonant tank consists of the inductor/antenna, three band switching capacitors and two tuning varactors. In order to increase the output voltage swing, transistor sizing is employed to adjust the bias current instead of using a current source. A power amplifier is not required for short range communication.
The VCO design is based on a simultaneous transconductance \( g_m \) and impedance matching technique. This approach reduces the flicker noise, improves output signal power and VCO phase noise performance. To maximize the output power in the complementary VCO, the voltage swing has to be maximized. This can be achieved by setting the dc operating voltage at the resonator to half of the drain voltage (VDD) by matching the \( g_m \) of the PMOS to that of the NMOS. For \( g_m \) matching, the PMOS width is kept 2.5 times that of the NMOS as a rule of thumb to account for lower mobility in PMOS devices. The gate lengths of NMOS and PMOS are identical in this case. However, for simultaneous \( g_m \) and impedance matching, the length of the...
PMOS is chosen to be the minimum possible gate length whereas for NMOS a larger gate length is used. The widths for both types of transistors are estimated analytically and then optimized through circuit simulation.

The MOS varactors employed in this work exhibit the maximum tunability for a biasing range of -0.2 to +0.2 V. Since the sensor data will modulate the carrier frequency through the control line of these varactors, maximum TX sensitivity will be achieved by providing control signal in this biasing range. The band switching capacitor bank comprises three Metal Insulator Metal (MIM) capacitors. Provision has been made to disconnect two of these MIM capacitors, in the case of wide fabrication tolerances. This can switch the operating band from 5 GHz to 5.25 GHz or 5.5 GHz respectively. The varactors can provide a fine tuning of ± 200 MHz around any of these bands. The VCO outputs are buffered through cascaded inverters as shown in Figure 3.14. The three stage buffer on either side of the differential circuit ensures minimum loading of the VCO core. The buffers are included only for measurements or connection to an external antenna, and will remain off during the normal operation of the Soc transmitter. A separate bias line for the buffers ensures that the buffers are turned on only when required. The simulated time domain output of the VCO through the buffers is shown in Figure 3.15, which confirms the 5.2 GHz frequency of operation. The post layout simulations of the VCO demonstrate a phase noise of -118 dBc/Hz at 1MHz offset as shown in Figure 3.16. The phase noise is strongly dependent on the Q of the on-chip inductor, which if increased will turn the inductor into a poor radiator.
Figure 3.14 Buffer schematic

Figure 3.15 VCO time domain output through the integrated buffer
Figure 3.16 VCO simulated phase noise

Layout and Fabrication

The chip microphotograph is shown in Figure 3.17. Its size is 1 x 1.5 mm$^2$, which is the smallest reported TX chip with an on-chip antenna for the 5 GHz band. The antenna is placed in the centre with two sides close to the chip edges and having no active circuitry, or bond pads in close vicinity. A metal width of 100 μm is employed which is more than the 25 μm maximum permissible metal width for the top metal layer. The violation of this design rule was achieved by inclusion of an additional layer on top of the antenna. The VCO is placed in the centre of the loop antenna and has a guard ring protection for noise suppression (not shown in Figure 3.17). A separate set of bond pads is provided for passive inductor testing. The VCO can be tested through the two buffers at the differential outputs. Electrostatic discharge (ESD) structures have been implemented with all the bond pads for protection. Appropriate microsurgery points have been incorporated in the layout for isolating and testing different structures independent
of each other. Metal is inserted in order to meet the metal fill density specifications of the process. However, care has been taken that no top metal layer is filled close to the antenna, and the least amount of metal is placed inside the loop.

![Microphotograph of VCO TX with on-chip antenna](image)

**Figure 3.17 Microphotograph of VCO TX with on-chip antenna**

**Measurements**

The modified on-chip antenna gain and radiation pattern are measured with the same technique described in section 3.2.1, however, this time the TX chip is not mounted on a PCB. Instead, the measurements are done on bare die glued to a glass plate as shown in Figure 3.18. A custom stand is used to measure the radiated power at different angles and the scanning is done manually. A measured gain of -22 dB is achieved, which is consistent with the previous on-chip antenna measurements. The measured radiation pattern is given in Figure 3.19. It is significantly improved from the previous measured radiation pattern as the maximum radiation is achieved along the plane of the loop (± 90°), as expected. This confirms the validity of the
design precautions applied to this chip. There is, however, still a difference of 3 to 4 dBs between the levels of each radiation pattern peak. The asymmetry can be attributed to measurement error, namely the presence of metal obstructions at +90°.

Figure 3.18 On-chip antenna (a) radiation pattern measurement setup (b) zoom in of probe feeding
The VCO draws an average current of 2.8 mA and consumes 3.3 mW of power from a 1.2V supply. The power dissipation, in general, is higher for differential circuits; however with high Q inductors it can be reduced. The power dissipation can also be reduced by using a lower current value at the expense of reduced output power and range. The oscillation frequency measurement done on a spectrum analyzer via the output buffers is shown in Figure 3.20. It confirms the frequency of operation to be 5.26 GHz as designed. A phase noise of -107 dBc/Hz is measured at 20 MHz offset, and is shown in Figure 3.21. As previously discussed, such phase noise performance is expected with the relatively low Q inductor/antenna employed.
Figure 3.20 TX VCO measured response

Figure 3.21 Measured phase noise
With the integration of a suitable power source, the complete wireless dosimeter can be smaller than a dime as shown in Figure 3.22.

![Demonstration of wireless dosimeter](image)

**Figure 3.22 Demonstration of wireless dosimeter**

### 3.3 RX Side On-chip Antenna

This section presents an on-chip antenna design for a monolithic receiver chip realized in a standard 0.13um CMOS process. This work was done collaboratively with fellow PhD student Muhammad Arsalan who designed the circuits for the receiver chip. The on-chip antenna has been conjugately matched to the differential Low Noise Amplifier (LNA) for a wide frequency range through co-design of the circuits and antenna. In order to optimize the chip space, the circuits are placed inside the antenna as shown in Figure 3.23.

Recently, many RX SoC designs have been reported which employ on-chip antennas [36][107][108]. However, all these designs are for very high frequencies where on-chip antenna
design presents fewer challenges due to size. In a demonstration of a 20 GHz RX chip with an on-chip antenna [109], a relatively large antenna (3 mm long) is integrated with the LNA, but is not fully characterized. A 24 GHz receiver design with an on-chip antenna is shown in [37], but it makes use of a non-standard high resistivity SiGe substrate. Recently a 5 GHz slot antenna design has been presented [59] with shielded ground plane to improve the on-chip antenna efficiency. This design, however, occupies large chip space (4 mm$^2$) and the on-chip antenna has not been optimized to conjugately match the LNA complex input impedance. Moreover the antenna is not characterized for its radiation pattern, which is one of the most important and challenging parts of on-chip antenna design. Most of the previous work does not exploit on-chip antenna and LNA co-design for simultaneous low noise and input power conjugate matching, relying instead on traditional 50 Ω matching schemes. Moreover, it either employs non-standard high resistivity substrates or additional post processing steps. Most of the antennas and chip sizes are quite large for their frequency of operation; no attempt is made to place the circuits inside the antenna, or account for the effects of antenna and circuits in close proximity. The on-chip antennas are seldom characterized for their radiation characteristics.

![Figure 3.23 RX side on-chip folded dipole](image)

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3.3.1 Design

The LNA and antenna are designed interactively to conjugately match the impedance without the need for matching components. This eases the stringent requirements of matching both the antenna and LNA to 50 Ω. Initially the LNA is designed for the simultaneous Noise Figure (NF) and input power matching. This results in a complex LNA impedance with a large real part. The on-chip antenna is then designed to conjugately match this complex impedance, however the real part of its impedance does not readily match that of the LNA. This is because the resistance of on-chip antennas realized in low resistivity Si is typically quite small [17]. Therefore, the LNA impedance is tuned to reduce the real part, resulting in a slightly higher NF and lower gain while easing the conjugate matching.

HFSS simulations are used in designing the on-chip antenna. The on-chip antenna is realized in the 4 μm thick top Al metal layer. A dipole antenna is chosen in order to drive the differential LNA without a balun. The dipole arms are folded to fit into a chip space of 1.3 mm x 1 mm. Since the LNA is placed inside the dipole antenna in the final layout, it is fed through two internal lumped ports in HFSS to replicate the LNA connection with the antenna.

The LNA’s optimized differential impedance at 5.2 GHz is 91 + j124 Ω, and the on-chip antenna is designed to conjugately match to this impedance. This is accomplished by lengthening the dipole antenna. However, this mostly increases the loss resistance instead of the radiation resistance of the antenna. The trade-off in matching to a large LNA real impedance is a reduced antenna gain. It is observed that increasing the metal width increases the antenna gain, however due to fabrication constraints, it is limited to 100 μm. Care has been taken that, in the available chip space, the gap between the conductors is sufficient so that oppositely directed current does
not cancel the radiated fields. Nonetheless, due to the lossy nature of the Si substrate, this effect is minimal. In simulations, a sensitivity analysis is done to choose suitable locations of the LNA elements with respect to the antenna so as to achieve minimum spacing between the various elements. The final dimensions of the antenna are 1.3 mm x 0.7 mm, resulting in a differential impedance of 90 - j133 Ω at 5.2 GHz. This yields an excellent match between the on-chip antenna and the LNA impedances over a broad bandwidth, as shown in Figure 3.24. It is worth mentioning here that the co-design of antenna and LNA has helped to achieve a wide impedance bandwidth. Simulations reveal a bore-sight maximum radiation pattern with a gain of -35 dBi. It is also observed in simulations that placing the antenna closer to the chip edges slightly increases the gain.

Figure 3.24. Simulated S11 of on-chip antenna (referenced to complex impedance of LNA)
3.3.2 Fabrication and Measurements

Since the circuits are placed inside the antenna, there are several challenges associated with the layout of the chip. Placement of several inductors inside a small area without affecting the performance of the circuits or the antenna, and facilitating independent testing of different sub-modules, are the most difficult aspects. Also, routing the bias, signal and ground traces to the pads through a complex circuit without breaking any design rules is difficult. Nonetheless, insight gained from EM and post layout circuit simulations and inclusion of microsurgery points eases some of these challenges. Another consideration is to make the layout as symmetric as possible to ensure true differential operation. As shown in the microphotograph (Figure 3.25), of the realized chip the antenna remains close to the chip edges with minimal interference from nearby metals.

Figure 3.25. Microphotograph of the receiver chip
As was seen with the two previous SoC designs, experimental characterization of the radiation properties of the on-chip dipole antenna is challenging. A moveable microscope with a custom stand is employed to perform the measurements. A transmitter patch antenna with gain $G_p$ is mounted on the stand which can rotate around the receiver chip. It is fed through the signal generator with a known transmit power $P_t$. The power is received at bore-sight by another patch antenna placed on the probe station chuck and recorded through the spectrum analyser as $P_{rp}$. The receive patch antenna is then replaced by the receiver chip while the rest of the setup remains the same. The power received by the on-chip antenna, after being amplified by the LNA, is measured and is denoted as $P_{rc}$. The on-chip antenna gain $G_c$ can now be calculated through (3.4), where $\text{LNA}_q$ is the amplifier gain obtained from a separate measurement of the micro-surgically disconnected LNA [23].

$$G_c = P_{rc} - P_{rp} + G_p - \text{LNA}_G$$  \hspace{1cm} (3.4)

The measured antenna gain from (3.2) is -35 dBi, which is 0.25 dB of the simulated antenna gain. In simulations, it is observed that the on-chip antenna gain varies from -45 dBi at 3 GHz to -25 dBi at 10 GHz. The measured radiation pattern is shown in Figure 3.26, and seen to be in good agreement with the simulated radiation pattern of the dipole antenna.
3.4 RF SoC Design Issues

Following the design and experimental work conducted in this chapter, it is important to highlight the major challenges and issues involved in advanced RF SoC development. These points will be useful for continued research on the topic.

1. No single simulation tool can handle the SoC design efficiently. Therefore, a co-design methodology is required through EM, microwave and circuit simulators to tackle this multi-domain problem.

2. Antenna is not typically on-chip, therefore its layout along with circuits, and metal fill is challenging. Since there are no dedicated metal layers or rules for on-chip antennas, many Design Rule Checks (DRC) result in errors. These have to be tackled in unique ways. An example is that the antenna's large metal width connected to the transistors...
violates the antenna rule. This error is resolved by providing a ground connection to one of the antenna arm. This ground connection must be removed through microsurgery (laser) before the measurements.

3. Parasitic coupling from circuits, inductors, and nearby bond pads can deteriorate antenna’s performance so their placement with respect to antenna has to be carefully investigated in EM simulations.

4. Interference in circuits due to nearby radiator element could not be investigated in post layout circuit simulations, due to the simulator’s limitations.

5. Placement of close by inductors requires the currents to be in opposite directions in order to cancel the mutual coupling between them as shown in Figure 3.27.

6. Undesired coupling through the substrate must be blocked through guard rings around circuits and inductors.

7. It is hard to plan metal fill till the layout is near completion, therefore metal fill must be done with back and forth simulations in EM and circuit simulator a shown in Figure 3.28.

8. Tuning elements are added to compensate for any process variations. For example the band switching capacitors in the TX VCO are designed to adjust the operational frequency if required.

9. On-chip antenna radiation characteristics cannot be measured in anechoic chamber unless the chip is mounted on a board. Mounting the chip results in erroneous results
because of blocking and interference from other components as observed in Figure 3.10. It is therefore better to measure the radiation pattern on the bare die. However, this requires custom setup and careful use of probes.

Inductors placement

Metal fill

Figure 3.27 SoC design issues

Metal fill Check in EM Sims

Figure 3.28 SoC design issues (metal fill)
3.5 Summary and Contribution

In fulfillment of the first three objectives of the thesis, this chapter has presented three novel SoC designs having on-chip antennas combined with RF transmitter and receiver circuitry. A highly integrated, low power CMOS VCO TX has been demonstrated for short range wireless radiation sensor applications. The VCO tank inductor has been optimized to act as an on-chip inductor-antenna, thus minimizing chip area. Its 0.5mm$^2$ size is the smallest reported on-chip antenna in the UN II band. This is the first ever demonstration of experimental characterization of an on-chip inductor/antenna for its radiation properties. The tradeoffs in the design and challenges in the experimental work have been highlighted. The complete TX chip sized 1.5mm$^2$ consumes 3.3 mW of power and can communicate with a low noise receiver connected to a patch antenna 2 m away from the TX. With the integration of a suitable power source, the complete wireless dosimeter can be smaller than a dime as shown in Figure 3.22. On the RX side, co-design of on-chip dipole antenna and LNA has been demonstrated for conjugate matching. These results represent the first contribution of this thesis, namely ‘Oscillator TX with On-chip Inductor/Antenna’.

The work of this chapter has led to many publications. One journal [9] and seven conference papers have already been published [11-15][17][18]. One more journal paper has been accepted recently [23].
Chapter 4

4 RF LTCC SoP

SoC, while highly miniaturized, has a number of limitations as was described in Sec 3.4. Excellent miniaturization of RF electronics is possible through innovative SoP designs to achieve compact yet efficient wireless systems. Within the SoP domain, LTCC can offer numerous advantages, including the possibility of using an arbitrary number of layers to embed passives and enable vertical integration of RF components within a single module. Moreover, the low loss nature of LTCC substrates makes them very suitable for efficient antenna design. This chapter will investigate innovative ways to package RFICs in order to make the overall wireless dosimeter system compact, low power and efficient. In accordance with the fourth and fifth objectives of this thesis, two 5 GHz SoP designs are proposed in this chapter. An LTCC TX package with a conventionally connected antenna will first be described. This will serve as a reference design for a second LTCC TX package having a highly innovative aperture coupled antenna. Finally, to fulfill the six objective of the thesis, an analytical model for the antenna coupling scheme of the latter design will be given.
4.1 Conventional LTCC package with antenna

The oscillator TX chip described in section 3.2.2 has been shown to work independently through its on-chip antenna, although its range was limited due largely to poor antenna gain. One way to enhance the range for applications like EVARM is by employing an efficient package antenna in a low loss medium. The chip has to be packaged in any case, so if the package houses an integrated antenna it can be connected to the chip through the conventional bond pad and bond wire arrangement, or through a flip-chip and solder balls option. Generally, the RF transceiver circuits are quite sensitive to this external loading and therefore require an isolating buffer amplifier in between the chip circuitry and the external components. A major advantage of integrated antennas is their ability to conjugately match the circuit’s impedance without any matching components. In this context, the LTCC antenna for the proposed SoP is designed to conjugately match the output impedance of the oscillator TX’s buffer amplifiers. Since the TX chip (the same one as in Sec. 3.2.2) has differential circuits, it is best to employ a differential antenna. Moreover, the antenna simulation must take into account the complete package along with the antenna as this is an attempt to co-design the two. With the buffer amplifiers turned on and properly matched to the package antenna, most of the power will be supplied to it and efficiently radiated. Nonetheless, some power will still be lost through radiation of the on-chip inductor, as it was originally optimized as an antenna.
4.1.1 LTCC antenna/package co-design

The proposed SoP's simulation geometry is shown in Figure 4.1. The module employs an efficient LTCC antenna in addition to having a cavity to accommodate the TX chip. In this work, the LTCC package with integrated antenna is designed in an eight layer (800 μm) thick Ferro A6-S process. The material properties of the LTCC tape system are listed in Table 4.1 [110]. This antenna must be connected to the TX VCO through the buffer amplifiers to avoid loading of the VCO. The buffer amplifiers exhibit a differential impedance of 32-j12 Ω, so the antenna is designed to provide a good return loss with reference to this impedance at 5.2 GHz. A dipole antenna is chosen and its arms are folded to optimize space consumption. The final antenna structure resulted in a differential impedance of 48+j25 Ω, which in turn provided a return loss of 13 dB at 5.2 GHz. The dipole displays a gain of -1 dB with a broadside radiation pattern as shown in Figure 4.2. The final SoP layout contains an additional cavity to house the sensor chip. The complete LTCC package, sized 1.6 cm X 1.6 cm, contains cavities with appropriate ground and supply connections for both the sensor and the TX chips. Both cavities are tailored to the respective chip dimensions and are five layers deep. The control signal line from the sensor to the TX chip is routed through the package, and wire bonded at each end. The package could easily accommodate a power source by means of a cavity formed on its backside, with the necessary interconnects embedded in the package. The fabricated package, mounted on a test board, is shown in Figure 4.3. The bias and ground connections are also provided through package interconnects.
Figure 4.1 HFSS Simulation Model for LTCC module

Table 4.1 Material Properties For Ferro A6 Ltcc Tape System [110]

<table>
<thead>
<tr>
<th>Material Property</th>
<th>Value</th>
</tr>
</thead>
<tbody>
<tr>
<td>Dielectric Constant</td>
<td>5.9 ± 0.2</td>
</tr>
<tr>
<td>Dielectric thickness (green tape)</td>
<td>127 μm</td>
</tr>
<tr>
<td>Dielectric thickness (fired)</td>
<td>90-100 μm</td>
</tr>
<tr>
<td>Loss Tangent</td>
<td>0.002</td>
</tr>
<tr>
<td>Conductor type</td>
<td>Silver and Gold</td>
</tr>
<tr>
<td>Conductor thickness</td>
<td>10 to 15 μm</td>
</tr>
<tr>
<td>Color</td>
<td>White</td>
</tr>
</tbody>
</table>
Figure 4.2 Simulated LTCC dipole radiation

Figure 4.3 Photograph of LTCC module
Testing of the LTCC SoP module was performed with the TX chip duly connected to the antenna through bond wires as shown in Figure 4.3. A horn antenna connected to a spectrum analyzer received the power from the wireless SoP module under test. Initially the buffer amplifiers were turned off and the power received through the on-chip antenna (SoC approach) was recorded. Then, the buffer amplifiers were turned on and power was measured through the LTCC antenna (SoP approach). Larger current is required in this case to operate the buffer amplifiers which were turned off in the SoC implementation. The wireless LTCC SoP was seen to provide 12 dB more transmitted power as compared to the SoC design. Though a substantial increase in TX power is observed, the power actually delivered to the LTCC antenna was lower than expected. This discrepancy is attributed to the mismatch loss resulting from the presence of bond wires (the simulation setup did not include the bond wires). It was not deemed necessary to perform more extensive testing of this LTCC SoP because 1) this is only a reference design, 2) the appropriate test structures (probe pads, etc) were not available. Nonetheless, assuming no mismatch loss, range calculations similar to the ones done for the SoC case (Section 3.2.1), reveal that the conventional LTCC SoP module can communicate up to a range of 75 m. This is a significant extension in wireless communication distance compared to the 2 m obtained with the SoC design. However, such an increase comes at the expense of increased DC power consumption from 3.3 mW to 38 mW due to the biasing required for the buffer amplifiers.
4.2 Aperture Coupled LTCC SoP

Previous SoP (section 4.1) demonstrated an increase in communication range with an efficient LTCC antenna, but with increased power consumption. Though, the enhanced communication range is attractive, but it is desirable to achieve it with minimal increase in power consumption. The aperture coupled LTCC SoP design is targeted towards the same goal. Generally, the RF circuits are connected to the feed line of an LTCC antenna through bond wires or solder balls as shown in the previous section. Typically, this arrangement requires an isolating buffer amplifier and bond pads on the chip, as well as impedance matching elements between the antenna and RF circuits. This approach not only adds to the number of design steps, cost and overall power consumption, but also makes the module less attractive due to the presence of bond wires.

An interesting approach to overcome the above limitations is to establish a wireless connection between the RF circuit and the LTCC antenna. Aperture coupling is a well established technique for non-contact or wireless feeding of microstrip patch antennas [111]. The conventional aperture coupled patch antenna is shown in Figure 4.4. Lately, an active integrated patch antenna fed with the aperture coupling technique has been demonstrated [112]. In addition, a silicon based aperture coupled patch antenna is demonstrated in [113]; however they both utilize a conventional microstrip feed line. This only eliminates the physical connection between the feed line and the antenna; the connections and components required between the integrated circuit (IC) and the antenna feed line cannot be removed. In [83], a parasitic coupling approach is demonstrated to couple an array of patches to the IC; however
this is done through a hypothetical IC and antenna. The measured results in [83] are obtained using a microstrip feed and via combination, which does not reflect the complexities of real chip-to-package coupling. This proposed design alleviates the above problems by a novel SoP implementation, which employs a wireless interconnect between the RF chip and the LTCC antenna as shown in Figure 4.5. This is done by electromagnetic coupling from the on-chip antenna to a coupling aperture or slot in the ground plane and eventually to the LTCC patch antenna. The design requires neither a buffer amplifier and connecting bond pad on the chip, nor matching elements or feed lines on the package. It also eliminates the requirement for a balun to connect differential circuits to the single ended antennas or vice versa. To the author's knowledge, this is the first ever LTCC aperture coupled patch antenna implementation with direct feeding from a TX on-chip antenna.

Figure 4.4 Conventional aperture coupled patch concept (fed through microstrip line)
4.2.1 Design and Simulation

The aperture coupled patch topology utilizes a common ground plane between the radiating antenna and the feed line [114]. For this work, aperture coupling is employed mainly because it will allow direct coupling of the TX on-chip antenna to the LTCC patch antenna without the need of a microstrip feed line. In addition, the buffer circuits can remain off. Also, the ground plane in between the patch antenna and the TX chip will act as a shield for the TX circuits. However, a limitation of this technique is that the slot in the ground plane can radiate considerably in the backward direction. This unwanted radiation can be minimized by choosing the optimum slot length with respect to the patch size.
The Ferro A6-S LTTC tape system is again employed in this design. Each layer has a fired thickness of 100 μm. The substrate is chosen to be 8 layers thick because it will house a 300 μm thick RF chip in a cavity. The cavity thickness is chosen to be 600 μm to accommodate the chip and the biasing bond wires. The LTCC fabrication rules require a minimum of two layers beneath the cavity, thus resulting in a total substrate thickness of 800 μm. The superstrate which will contain the antenna can be of any other LTCC material, however for simplicity the same LTCC tape system is used for the antenna as well.

The design procedure is as follows. First, a conventional aperture coupled patch antenna with a microstrip feed line is simulated in HFSS. This determines the approximate size of the patch antenna at 5.2 GHz, the feed location and the slot dimensions. Next, the microstrip line is replaced with the TX chip. The design is optimized for maximum coupling between the on-chip antenna and the LTCC patch antenna through the slot in the ground plane. This maximizes the overall gain of the TX module. The thicknesses of the air gap and the superstrate determined this way are an initial estimate of the design and will change during the final optimization. The patch antenna dimensions of 1.7 cm x 1.7 cm are obtained in simulations. The substrate, superstrate and ground plane dimensions are 2cm x 2cm. The feed line is placed below the centre of the patch antenna to maximize magnetic field coupling.

After determination of the approximate patch size and feed point location, the microstrip feed line is replaced with the TX chip. The chip is placed in a cavity sized 4.8mm x 3.8mm exactly at the location where the microstrip line fed the patch. The size of the cavity is chosen so as to leave enough room for the power routing and bond wires after placing the chip in the
cavity. The cavity size remains the same for the lower four layers, however it is made the same width as that of the slot in the ground plane for the top two layers. This is done to avoid fabrication complexities. The patch antenna is on the bottom-most layer of the superstrate. The air gap is realized through four corner posts made of the same LTCC tape system as the substrate. The layer by layer layout of the aperture coupled module along with the final dimensions is shown in Figure 4.6. The cross-sectional view of the module is shown in Figure 4.7. The bottom 6 layers of the substrate are fired together, whereas the top two layers (layer 7 and 8) are fired separately. This is done in order to ease the placement and wire bonding of the chip in the cavity. The top two layers of the substrate, along with the four corner posts and superstrate are glued to the substrate after the placement of the chip. The power and ground pads in the cavity connect to the pads on the bottom of the substrate through vias. The bottom pads can be connected to the contacts of a custom made lithium polymer battery. The battery would have the same lateral dimensions as that of the substrate and it could be simply glued to the bottom of the substrate as shown in Figure 4.7.

The design is sensitive to a number of parameters, the most important being the location, length, and width of the slot in the ground plane. Other important parameters are the air gap and superstrate thicknesses. Extensive parametric simulations are required to optimize many parameters at the same time. The goal is to maximize the gain of the module by efficient coupling between the on-chip antenna and the LTCC antenna through the slot in the ground plane, without affecting the RF properties of the circuit. Initially, keeping the slot length and width the same as that of the microstrip fed case, the thicknesses of the air gap and superstrate are optimized. After achieving a reasonable gain value, the thicknesses are kept constant and
the slot length and width are optimized. It is observed in simulations that extending the slot length to the extreme right edge of the substrate results in maximum gain (this behaviour is investigated analytically in section 4.3). Finally, the thicknesses of the air gap and superstrate are optimized again with the new slot dimensions. It is worth mentioning that this technique works on the near field coupling and thus the far field radiation pattern of the on-chip antenna is insignificant here.

A combination of air gap thickness of 2 mm and superstrate thickness of 1.8 mm increases the gain of the module from the on-chip antenna gain of -34 dBi to 0.5 dBi. This remarkable result is achieved without any physical connection or elaborate matching of the RF circuit to the external antenna. However, the superstrate thickness of 1.8 mm (18 LTCC layers) is not an economically viable solution because it does not contain any other passives except the patch antenna. Therefore the design is re-optimized for a thinner superstrate by compromising somewhat on the gain. The final superstrate thickness of 0.2 mm, with an air gap thickness of 2.4 mm, yields a gain of -2.3 dBi. This gain is still 32 dB more than that of the on-chip antenna gain.
Figure 4.6 Layer by layer description of the complete LTCC TX module

Figure 4.7 Cross-sectional view of the complete LTCC TX module

Figure 4.8 shows the gain and radiation pattern of the LTCC aperture coupled patch antenna. The back lobe is reduced to a level approximately 10 dB lower than the front lobe by optimizing the slot length. The on-chip antenna/inductor’s RF performance has been affected slightly but is still within acceptable operational limits of the TX module. Figure 4.9 compares the L and Q of the on-chip inductor with and without coupling to the slot and the patch.
antenna. A clear notch can be seen in both the L and Q curves at the frequency of interest, which shows the coupling; however, the deviation from the nominal values is not detrimental.

![Diagram](image)

**Figure 4.8** Aperture coupled LTCC patch antenna gain and radiation pattern

![Diagram](image)

**Figure 4.9** TX VCO inductor performance with and without aperture coupling
The variation of the antenna gain with respect to the thickness of the air gap, while keeping other parameters constant, is shown in Figure 4.10. It shows that a fabrication tolerance of up to 300 μm is permissible without affecting maximum gain. Table 4.2 compares the performance of the three TX modules developed in this thesis. All modules utilize a receiver with a sensitivity of -70 dBm which is attached to an antenna having a gain of 6.5 dBi. It is evident that the proposed aperture coupled LTCC module is the best solution in terms of achieving a balance between communication range and power consumption. From the Friis formula, the aperture coupled design provides 22 m more range than the TX with on chip antenna, without increasing the power consumption. The conventional LTCC package, on the other hand, provides 3 times more range than the proposed design but consumes 12 times more power.

![Figure 4.10 LTCC antenna gain versus air gap thickness for aperture-coupling](image-url)

Figure 4.10 LTCC antenna gain versus air gap thickness for aperture-coupling
Table 4.2 Performance Comparison for Different TX Modules

<table>
<thead>
<tr>
<th>Module Type</th>
<th>Power Consumption</th>
<th>Gain</th>
<th>Range</th>
</tr>
</thead>
<tbody>
<tr>
<td>Stand alone TX chip</td>
<td>3.3 mW</td>
<td>-34 dBi</td>
<td>2 m</td>
</tr>
<tr>
<td>TX chip in conventional LTCC package</td>
<td>38 mW</td>
<td>-1 dBi</td>
<td>75 m</td>
</tr>
<tr>
<td>TX chip in proposed LTCC package</td>
<td>3.3 mW</td>
<td>-2.3 dBi</td>
<td>24 m</td>
</tr>
</tbody>
</table>

4.2.2 Fabrication and Measurements

Since the aperture coupled module requires the TX chip to be placed in a cavity embedded underneath two layers and a ground plane, it cannot be fabricated as a single piece without subjecting the TX chip to high firing temperatures. Also the fabrication complexities do not allow simultaneous firing of the LTCC layers with the ground plane, the four posts and the superstrate with patch antenna. Therefore the module is fabricated in four parts, (1) the 6 substrate layers with a cavity, (2) the 7th and 8th substrate layers with ground plane, (3) the four corner posts, and (4) the two superstrate layers with integrated patch antenna.

The next step is to place the TX chip in the cavity. This is done by utilizing silver epoxy in the cavity and baking the substrate with the TX chip at 150° C. The TX chip is now wire bonded to the bias pads. After the placement of the chip and wire bonding, the remaining substrate layers with ground plane are placed on top of the chip in the cavity. Then the LTCC posts are positioned on the four corners of the ground plane and the superstrate with patch antenna is supported on these posts. All the bonding between the different parts of the modules is
achieved through the silver epoxy and baking process. The individual components, the sequence of their integration and the final module are shown in Figure 4.11.

Figure 4.11 TX aperture coupled SoP (a) TX chip placed in LTCC substrate (b) ground plane with slot and LTCC post placed on substrate with the TX chip (c) superstrate with patch antenna placed on the rest of the module (d) complete SoP module

In order to measure the relative increase in gain for the LTCC aperture coupled module as compared to the TX chip with on-chip antenna, the latter is placed in cavities of two similar LTCC substrates. One of them is left open from the top (Figure 4.11 a) whereas the other has all the parts of the module in place (Figure 4.11 d). A horn is employed as the receive antenna and is connected to a spectrum analyzer. First, the received power is measured from the module with the on-chip antenna radiating into free space, and then the same is done for the module where the on-chip antenna radiates into the slot that couples to the patch antenna. The difference in the measured power levels indicates that the aperture coupled module has 10 dB more gain as compared to the TX chip alone. The radiation pattern of the module is measured.
through a custom jig, which rotates the receive antenna around the TX SoP and records the level of power at different angles. The normalized radiation pattern is shown in Figure 4.12. The measured radiation pattern shows a bore-sight maximum which is expected if the patch mode is excited. Consistent with simulations, the module which contains the uncovered TX chip demonstrates the maximum radiated power to be along the chip edges or 90° from the bore-sight. However, the same module, when covered with the rest of the SoP components displays the maximum radiated power to be at bore-sight. This shift in radiation pattern confirms the desired operation of the aperture coupled patch antenna. The measured radiation pattern shows a rather sharp main beam, with a 3 dB beamwidth of approximately 60°. This is slightly narrower than the conventional patch antenna’s 3 dB beamwidth, but this is expected due to the patch’s finite ground plane. However, the most attractive feature of this design is that the 10 dB increase in the TX SoP radiated power as compared to that of the SoC approach comes without any increase in DC power consumption. It was observed in the measurements, that both the designs, SoC and aperture coupled LTCC SoP, consume 3.3 mW of DC power.

![Figure 4.12 TX SoP measured radiation pattern](image-url)
Though the measured relative gain is less than what is observed in simulations, a number of factors explain this result. It has been observed in simulations that the design is quite sensitive to many parameters, in particular to the thickness of the air gap, length and width of the slot, placement of the chip with respect to the slot and the position of the posts on the ground plane. Close inspection and thickness measurements of the fabricated modules revealed that there are many things which are not according to the simulation model. Firstly, the substrate thickness is 0.734 mm which is less than the simulated 0.8 mm. The four posts height, which is responsible for the air thickness, varies between 2.2 to 2.3 mm instead of 2.4 mm. Moreover, the slot width is not uniform for the entire length as can be clearly seen in Figure 4.13. The slot becomes wider over the cavity as compared to the regular substrate. The cavity itself has rounded corners, contrary to the original design. Furthermore, the deposition of silver epoxy is done manually, so the thickness and uniformity could not be controlled as shown in Figure 4.13. It not only reduces the distance between the on-chip antenna and the slot but also causes the chip to be slightly tilted. Similar issues are observed in the manual placement and gluing of the four posts. Finally, this particular fabricated TX chip is working at 5.3 GHz which is different from the LTCC package design frequency of 5.2 GHz. All these measured discrepancies were subsequently checked in simulations and the simulated results verified the lower gain value in measurements. However, by adequately addressing the tolerance issues in fabrication and automating the postprocessing process, the optimum results predicted in simulations can be achieved with ease. Continuing maturity of LTCC fabrication processes should remedy this situation.
4.3 Analytical Modeling of Chip Antenna Aperture-Coupling

The aperture coupled patch antenna fed through a microstrip line has been extensively modeled. The initial model developed by Pozar made use of the cavity model of the patch antenna and the small hole coupling theory [111]. He later demonstrated an analytical model based on the reciprocity method [115]. This was followed by many investigations based on different methods like the moment method [116], cavity technique [117][118] and transmission line analysis [119]. A simple analytical model described in [120] employs an optimization technique but can only be used for initial approximate predictions. A full wave analysis using the spectral domain approach was reported in [121]. However, all these models deal with a microstrip feed of the aperture coupled patch, which is not the case here. In order to model the coupling through an on-chip loop antenna instead of a microstrip line, a simple analytical model is derived here. The principle of the method is similar to the reciprocity theorem.

With reference to Figure 4.5, the fields from the on-chip loop couple to the slot in the ground plane, and from the slot they couple to the patch antenna. The latter coupling is identical to previous implementations and thus the new analytical model need not investigate
it. The coupling between the on-chip loop antenna and the slot in the ground plane is the focus of this analysis. The goals are to 1) find the effect of a slot opening in the ground plane on a conducting loop near it, 2) obtain an expression to quantify the coupling from the loop to the slot, and 3) determine the optimum position of the loop with respect to the slot for best coupling.

Consider a conducting loop near a ground plane with excitation current $J_1$, enclosed in a hemisphere with surface $S$ and volume $V$ as shown in Figure 4.14. Let us assume that the electric and magnetic fields in the hemisphere, due to source $J_1$, are $E_1$ and $H_1$ respectively. For this case, it is assumed that there is no slot in the ground plane as shown in Figure 4.14 (a). Let the length of source $J_1$ to be denoted as $\Delta l$. Since $\Delta l$ is quite small, $J_1$ is assumed to be equal to a constant current density $J_0$. For the second case (shown in Figure 4.14 (b)), a slot of length $l_s$ and width $w_s$ is present in the ground plane. The electric and magnetic fields, due to excitation source $J_2$, are denoted as $E_2$ and $H_2$ respectively. Consistent with the first case, $J_2$ is assumed to be equal to $J_0$. Applying Maxwell equations to both cases,

**Case 1**
\[
\begin{align*}
\nabla \times E_1 &= -j \omega \mu H_1 \\
\nabla \times H_1 &= j \omega \varepsilon E_1 + J_1
\end{align*}
\]  
(4.1)  
(4.2)

**Case 2**
\[
\begin{align*}
\nabla \times E_2 &= -j \omega \mu H_2 \\
\nabla \times H_2 &= j \omega \varepsilon E_2 + J_2
\end{align*}
\]  
(4.3)  
(4.4)

Multiplying both sides of (4.1) with $H_2$ and (4.2) with $E_2$:

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\[ H_2 \cdot (\nabla \times E_1) = -j\omega\mu H_1 \cdot H_2 \]  
\[ E_2 \cdot (\nabla \times H_1) = j\omega\varepsilon E_1 \cdot E_2 + J_1 \cdot E_2 \]  

Similarly, multiplying both sides of (4.3) with \( H_1 \) and (4.4) with \( E_1 \):

\[ H_1 \cdot (\nabla \times E_2) = -j\omega\mu H_2 \cdot H_1 \]  
\[ E_1 \cdot (\nabla \times H_2) = j\omega\varepsilon E_2 \cdot E_1 + J_2 \cdot E_1 \]

**Figure 4.14** Problem definition (a) Case 1 with no slot (b) Case 2 with slot
Subtracting (4.8) from (4.5), and (4.7) from (4.6):

\[ H_2 \cdot (\nabla \times E_1) - E_1 \cdot (\nabla \times H_2) = -j \omega \varepsilon E_2 E_1 - J_2 E_1 - j \omega \mu H_1 H_2 \]
\[- \nabla \cdot (E_1 \times H_2) = j \omega \varepsilon E_2 E_1 + J_2 E_1 + j \omega \mu H_1 H_2 \]  
(4.9)

\[ E_2 \cdot (\nabla \times H_1) - H_1 \cdot (\nabla \times E_2) = j \omega \varepsilon E_2 E_1 + J_1 E_2 + j \omega \mu H_1 H_2 \]
\[- \nabla \cdot (E_2 \times H_1) = j \omega \varepsilon E_2 E_1 + J_1 E_2 + j \omega \mu H_1 H_2 \]  
(4.10)

Subtracting (4.10) from (4.9):

\[- \nabla \cdot (E_1 \times H_2 - E_2 \times H_1) = J_2 E_1 - J_1 E_2 \]  
(4.11)

Equation (4.11) is consistent with reciprocity theorem, without the magnetic sources [122].

Applying this to the complete hemisphere:

\[ \int_{s}(E_1 \times H_2 - E_2 \times H_1) \cdot ds = \int_{v}(E_1 \cdot J_2 - E_2 \cdot J_1) \cdot dv \]  
(4.12)

\[ S = S_\infty + S_g + S_{slot} \]

The integral over the remaining surface \((S_\infty)\) and the ground \((S_g)\) is zero. Also \(E_1\) is zero over the slot surface \(S_{slot}\) because the slot is not present in the first case. Therefore (4.12) can be simplified as follows:

\[ \int_{slot}(- E_2 \times H_1) \cdot ds = \int_{v}(E_1 \cdot J_2 - E_2 \cdot J_1) \cdot dv \]  
(4.13)

Since, the analysis is based on the assumption that the source current density stays constant \((J_1 = J_2 = J_0)\), the coupling between the slot in the ground plane and the conducting loop will be
reflected as a change in the source voltage. Let us assume that $V_1$ represents the source voltage in case 1 and $V_2$ the source voltage in case 2, and the change in the voltage is denoted as $\Delta V$.

Since the excitation current is only defined over the feed gap and is zero elsewhere, the volume integral is limited to the area of the feed gap $\Delta l$. Equation (4.13) can now be written as:

$$\int_{\text{slot}}(-E_2 \times H_1) \cdot ds = E_1 \Delta l \cdot \Delta s J_1 - E_2 \Delta l \cdot \Delta s J_2$$

$$\int_{\text{slot}}(-E_2 \times H_1) \cdot ds = E_1 \Delta I_1 - E_2 \Delta I_2$$

Where $I_1$ and $I_2$ are the currents in case 1 and case 2 and are equal to a constant current $I_0$. $\Delta s$ represents the surface area of the loop feed gap. Now the loop terminal voltages are found through:

$$\int_{\text{slot}}(-E_2 \times H_1) \cdot ds = (V_1 - V_2) I_0$$

$$\int_{\text{slot}}(-E_2 \times H_1) \cdot ds = \Delta V I_0$$

$$\frac{1}{I_0} \int_{\text{slot}}(-E_2 \times H_1) \cdot ds = \Delta V$$  \hspace{1cm} (4.14)

This is an important conclusion as it relates the electric field of the slot in the ground plane to the loop's change in the voltage due to the coupling between them. In (4.14), $H_1$ can be found by applying image theory to the fields of case 1, as shown in Figure 4.15. This field is proportional to $J_0$ and is a function of the position of the loop. The electric field over the slot can be represented by (4.15), where $E_o$ is the amplitude of the slot's electric field [123].
\[ E_2 = E_0 \cos(\frac{\pi y}{l_z}) \hat{x} \]  \hfill (4.15)

Since \( d_z \) is in the z direction, (4.15) can be written as:

\[
\int_{\text{slot}} (-E_0 \cos(\frac{\pi y}{l_z}) \hat{x} \times H_1) \cdot ds = \Delta V I_o \\
\int_{\text{slot}} (-E_0 \cos(\frac{\pi y}{l_z}) H_y) \cdot ds = \Delta V I_o 
\]  \hfill (4.16)

Center of ground plan is set to (0,0,0)

Figure 4.15 Image theory for case 1 (with no slot)

\( H_y \) varies with the position of the loop and therefore (4.16) can evaluate the optimum relative position of the loop with respect to the slot for best coupling. From (4.16), it is clear that the position of the loop with respect to the slot must be unsymmetrical in order to have better coupling. If the loop is symmetrically located below the slot, the opposite directed fields will
cancel each other out. So it is better to have a non-symmetrical position for the loop, preferably near the edges of the slot. This is an interesting result which is totally different from the microstrip fed aperture coupled antenna where the microstrip feed must be in the centre of the slot to achieve best coupling [111]. This difference can be explained through Figure 4.16, where the fields for both cases 1) microstrip feed, and 2) the loop antenna feed are shown over the slot in the ground plane. It can be seen in Figure 4.16 (a) that the fields induced in the slot through the microstrip are in the same direction and hence a symmetrical position of the microstrip line with respect to the slot will enhance the fields. In contrast, Figure 4.16 (b) depicts that the loop antenna induces oppositely directed fields in the slot and hence a symmetrical position with respect to the slot will cancel these fields. The best position is almost near the edge of slot, which has also been observed in the HFSS simulations of section 4.2.1.

![Figure 4.16](image)

*Figure 4.16 Comparison of coupling between a microstrip feed and an loop antenna feed*

The near magnetic field of a small loop is the same as that of a short magnetic dipole and is well known [122]:

---

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\[
H_r = \frac{I_o s}{2\pi} e^{-jr} \left( \frac{jk}{r^2} + \frac{1}{r^3} \right) \cos \theta \\
H_\theta = \frac{I_o s}{4\pi} e^{-jr} \left( -\frac{k^2}{r} + \frac{jk}{r^2} + \frac{1}{r^3} \right) \sin \theta
\]

where 'I_o s' is the magnetic moment, 's' is the area of the loop. Transforming these spherical coordinates into cartesian coordinates,

\[
H_y = H_y^\wedge
\]

\[
H_y = \frac{I_o s}{2\pi} e^{-jr} \left( \frac{jk}{r^2} + \frac{1}{r^3} \right) \cos \theta \sin \sin \theta \sin \phi + \frac{I_o s}{4\pi} e^{-jr} \left( -\frac{k^2}{r} + \frac{jk}{r^2} + \frac{1}{r^3} \right) \sin \theta \cos \theta \sin \phi
\]

\[
H_y = \frac{I_o s}{4\pi (x^2 + y^2 + z^2)^{3/2}} e^{-j\sqrt{(x^2 + y^2 + z^2)^2}} \left[ 3 jk(x^2 + y^2 + z^2)^{3/2} + 3 - k^2(x^2 + y^2 + z^2) \right] (yz) \quad (4.17)
\]

Let us assume that 'd' is the vertical distance of the slot from the loop and it is placed at the coordinates shown in Figure 4.15. Employing image theory, it is assumed that a similar current source is present on the other side of the ground plane. The total field on the slot will be the superposition of the fields from both the loop and its image.

If the H field due to the loop is \(H_{y l}\) and due to its image is \(H_{y l}^i\), the total magnetic field \(H_{Ty}\) on the slot is:

\[
H_{Ty} = H_{y l} + H_{y l}^i \\
H_{Ty} = 2H_y
\quad (4.18)
If \( x_0, y_0 \) and \( d \) are the coordinates of the loop, then the relative distance between the loop and any position along the slot can be expressed as \((x-x_0, y-y_0, z-d)\). Inserting \( H_y \) of (4.17) into (4.18) yields:

\[
H_{y}(x,y,z) = \frac{2I_o s}{4\pi[(x-x_0)^2 + (y-y_0)^2 + d^2]^\frac{3}{2}} e^{-jk[(x-x_0)^2 + (y-y_0)^2 + d^2]^\frac{1}{2}} 
\times \left[ 3jk\left((x-x_0)^2 + (y-y_0)^2 + d^2\right)^\frac{3}{2} + 3 - k^2\left((x-x_0)^2 + (y-y_0)^2 + d^2\right) \right] (d(y-y_0))
\]

Inserting this magnetic field in (4.15) yields:

\[
I_0 \Delta V = \int_{\text{slot}} \left( -E_0 \cos(\pi y / l_s) \right) \frac{2I_o s}{4\pi[(x-x_0)^2 + (y-y_0)^2 + d^2]^\frac{3}{2}} e^{-jk[(x-x_0)^2 + (y-y_0)^2 + d^2]^\frac{1}{2}} 
\times \left[ 3jk\left((x-x_0)^2 + (y-y_0)^2 + d^2\right)^\frac{3}{2} + 3 - k^2\left((x-x_0)^2 + (y-y_0)^2 + d^2\right) \right] (d(y-y_0)) ds
\]

The current \( I_0 \) cancels out from both sides of (4.20). Taking the design values of \( d, s \) and \( l_s \) in (4.20) and plotting \( \Delta V \) against varying positions across the length of the slot, results in Figure 4.17. It can be seen that the maximum coupling happens close to both ends of the slot and the coupling goes to zero when the loop is exactly at the centre of the slot. HFSS simulation results of the same are also plotted for comparison. A good match between the two curves is obtained, which validates the simple analytical model. Many approximations (loop geometry, uniform current distribution) have been used in this model which can explain the discrepancy in Figure
4.17. Nonetheless, the model can provide a very good initial estimate of the on-chip antenna optimum position with respect to the slot in the ground plane.

![Figure 4.17 Comparison of coupling between the loop and the slot at various positions through HFSS and analytical model](image)

**Figure 4.17 Comparison of coupling between the loop and the slot at various positions through HFSS and analytical model**

4.4 RF SoP Design Issues

Following the extensive design work conducted in this chapter, it is important to highlight the major challenges and issues involved in advanced RF SoP development. These points will be useful for continued research on the topic.

1. SoP requires co-design of IC and package. This is achieved through simultaneous circuit and EM simulations.
2. Fine details must be considered in an SoP design. For example, the simulation model of package passives must include the bond wires, bond pads and the IC cavity to avoid any mismatch with the measured results.

3. The size of the conventionally-connected LTCC module could be further reduced if the sensor and TX ICs were placed inside the antenna. However, this would require considerable study of antenna-circuit coupling effects.

4. To reduce long simulation times, sensitivity analysis must be performed on limited parts of the module based on insight gained from EM/Circuit modeling as shown in Figure 4.18.

5. Complex packages, such as the aperture coupled SoP module, require frequent communication and coordination with the fabrication staff during the design phase to ensure the smooth realization. Many times the design was altered due to the fabrication limitations.

6. The aperture coupled module is a sensitive design; therefore the LTCC process tolerances and fabrication limitations have pronounced effects on its performance. Continuing maturity of LTCC fabrication processes should remedy this situation. Other multilayer technologies like Liquid Crystal Polymer (LCP) can also be explored.

7. For the aperture coupled module, bond wires for biasing could be avoided by employing solder balls in a flip chip arrangement. Thus, total removal of bond wires would be achieved.
8. Manual post processing of the LTCC modules, in particular the aperture coupled module, is not recommended.

![E Field [V/m]]

Figure 4.18 EM analysis used to determine area of high sensitivity

4.5 Summary and Contributions
Two RF SoP designs suitable for wireless biomedical applications have been presented. A novel LTCC based TX SoP implementation has been demonstrated which makes use of on-chip-antenna-to-LTCC-package antenna coupling through an aperture in the common ground plane. The strategy is useful as it eliminates the need for isolating buffers, bond pads, bond wires, matching elements, baluns and transmission lines. It not only reduces the number of components and simplifies SoP design but also consumes lower power. The chip coupling to LTCC patch antenna improves the TX module gain by 32 dB (in simulation) and range by 22 m as compared to the on-chip antenna alone, without affecting the RF circuit performance and power consumption. The conventional LTCC package provides 3 times more range than the proposed design but consumes 12 times more power. To the author’s knowledge, this is the
first ever LTCC aperture coupled patch antenna implementation with direct feeding from a TX on-chip antenna. A simple analytical method is described to model the new coupling between the on-chip antenna and the slot in the ground plane. The work in this chapter completes the second and third contributions of the thesis, namely 'LTCC SoP Design' and 'Novel LTCC SoP Analytical Model'.

The work in this chapter has resulted in one journal paper [10] and a conference paper [19]. Another journal paper has recently been submitted [22].
5 Tunable and Reconfigurable LTCC SoP

The novel LTCC SoP designs presented in chapter 4 of this thesis were successful in achieving compact and efficient wireless RF transmitters for biomedical applications. Further enhancements that can be considered for LTCC SoP are increased miniaturization and component tunability and reconfigurability. The introduction of ferrite material in the package not only helps in the miniaturization of the components but it also permits the control of the devices made from it. Ferrite allows the properties of the package to be dynamically altered, meaning that the package will have the ability to control the signals that are passing through it. Therefore ferrite LTCC is a perfect candidate for tunable passive elements. In accordance with the final thesis objective, this chapter investigates the suitability of ferrite LTCC for tunable and reconfigurable SoP designs. An experimental ferrite tape material will first be characterized, following which the development of novel tunable antennas will be presented. The properties of the ferrite LTCC material that was available for this work prohibit the use in the 5GHz band (as will be described in this chapter); therefore, the designs presented here are in the 12 GHz band. The System-on-Package (SoP) work is an attempt to push the package beyond merely
providing embedded passives, wiring, and physical protection: the package itself would become the device. This concept is useful for applications like DBS-TV (Direct Broadcast Satellite Television) reflect array, where reconfigurable coverage is required, or for multi-band wireless sensor systems.

### 5.1 Ferrite LTCC material characterization

Ferrite integration in the LTCC medium is a fairly new concept. A limited number of experimental ferrite tape materials are currently available and can be used as standalone systems or sandwiched between standard LTCC dielectric layers. It is therefore necessary to characterize these substrates for their material properties such as $\varepsilon_r$, $\mu_r$, dielectric loss tangents, and saturation magnetization. This section focuses on the extraction of these properties for an experimental ferrite LTCC tape system ESL 40012 [8]. Generally, material characterization of ferrite substrates has been limited to microwave properties and very little work has been done to explore their magnetostatic properties, which are equally important. Previous work that was performed at microwave frequencies could only extract the product of $\varepsilon_r$ and $\mu_r$, as well as the loss tangent [89]. In the present work, the individual values have been isolated independently using a cavity resonance technique. Magnetostatic characterization is also performed here, employing both solenoid and toroid transformers that are completely embedded in the LTCC material under test. The novel toroid transformer has been chosen to eliminate the end-effects and magnetic flux leakage that are associated with solenoid transformer designs.
5.1.1 Microwave Characterization

Microwave frequency characterization is required to extract $\varepsilon_r$, $\mu_r$ and the loss tangents of the LTCC ferrite substrate. The properties for the substrate in the unbiased state are obtained here; whereas, biasing considerations are discussed in the next section. These measurements are done in collaboration with XLIM, France [126]. Generally, transmission line methods are used to obtain the material parameters; they are wideband and simple, but are less reliable. In contrast, resonant cavity methods measure complex permittivity and permeability at discrete frequencies but are very accurate. The resonant method employed here has been applied in many studies and compared to many other methods [127]. This technique does not require any preparation of the sample (cutting, polishing, or metallization) and makes no theoretical approximations. The test substrate is inserted between the two halves of a cylindrical cavity. It is excited in the $\text{TE}_{01,2q+1}$ mode to minimize the measurement uncertainties. Using the $\text{TE}_{01,2q+1}$ ($2q+1 = 1, 3$ or $5$) modes, the electric field is parallel to the plane of the sample and has negligible values close to the gap between the sample and the cavity wall. Two cavities with resonant frequencies near 10 and 25 GHz have been used. In such a configuration, the resonant frequency and quality factor of the resonant cavity mode can be computed exactly. Based on iterative computation, the complex permittivity and permeability of the sample can be extracted from the measured resonant frequency and quality factor. The loaded quality factor of one of the $\text{TE}_{01,2q+1}$ modes is used to compute the power losses due to the metallic walls. In order to determine the permittivity and the loss tangent of the substrate we only need the measurement of the resonant frequency and quality factor of the cavity loaded with the sample. The uncertainties of $\varepsilon_r$ and $\tan\delta$ are due to the uncertainties of the measured quality.
factors and resonant frequencies and of the manufacturing tolerances of the cavity (radius and height) and of the sample thickness.

Two LTCC ferrite samples have been tested and characterized. In both cases, the unbiased state is considered, and the permeability $\mu_r$ is found to be 1. Due to the sample size constraints, the lowest measurement frequency was 9.86 GHz. It is well known that the initial permeability of the ferrite materials goes to 1 at frequencies higher than a few GHz, which is consistent with the measured results. Table 5.1 lists the $\varepsilon_r$ and $\tan\delta$ parameters for the two samples at the two measurement frequencies.

<table>
<thead>
<tr>
<th>Sample 1</th>
<th>Frequency (GHz)</th>
<th>Thickness $(t \pm dt)$ (µm)</th>
<th>$\varepsilon_r \pm \Delta\varepsilon_r$</th>
<th>$(\tan\delta \pm \Delta\tan\delta) \times 10^{-3}$</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>9.86</td>
<td>230 ± 10</td>
<td>13.70 ± 0.59</td>
<td>4.24 ± 0.37</td>
</tr>
<tr>
<td>Sample 2</td>
<td>27.2</td>
<td>230 ± 10</td>
<td>14.14 ± 0.65</td>
<td>1.11 ± 0.10</td>
</tr>
</tbody>
</table>

In addition to the resonant cavity method, a transmission line characterization technique has also been utilized with printed Coplanar waveguide (CPW) lines to assess the line losses for the ferrite under test. The calibration structures which were measured between 0.1 GHz and 14 GHz are shown in Figure 5.1. The attenuation constant $\alpha$ was extracted from the calibration structures built on the ferrite substrate and is shown in Figure 5.2.
Except for the 2 GHz to 9 GHz band, the $\alpha$ values of around 0.5 dB/cm confirm the low loss behavior of this material. However, the large loss observed in Figure 5.2, which peaks around 7 GHz, is due to the resonance of domain wall rotation inside the ferrite. It is a phenomenon that is related to low-field losses in unsaturated polycrystalline ferrites. For practical circuit applications, the domain wall resonance and associated loss would be removed by adequately magnetizing the ferrite material [128].

Figure 5.1 Fabricated ferrite LTCC structures
5.1.2 Microwave Characterization under Biased Conditions

In order to measure the ferrite LTCC microwave properties under biased conditions, the resonant cavity perturbation technique is employed [129], this time in an X-band rectangular waveguide cavity (RWC). The empty RWC is measured first for its S-parameters. Next the cavity is loaded with a very small sample of ferrite LTCC, which will perturb the resonance. From the change in the resonant frequency and Q of the cavity, the microwave properties (\(\varepsilon, \mu, \tan\delta\)) can be extracted. Similarly, measurements can be made for different magnetic biasing levels and therefore the material properties in these biased states can be extracted. The biasing is provided by two large external electromagnets.

Figure 5.2 Attenuation constant extracted from ferrite CPW line
For the electrical properties ($\varepsilon$, $\tan\delta_e$), the sample has to be placed in the center of the cavity where the electrical field is maximum and the magnetic field is zero. The sample must fit exactly in the height of the RWG cavity for uniform fields and to avoid complex matching problems. For the magnetic properties, the sample has to be placed at the end of the cavity (short circuit) where the magnetic field is maximum and the electric field is zero. The sample has to be very small and uniform for the magnetic property measurements.

To hold the sample in the RWC, the ferrite is placed in styrofoam and inserted through the back end. It is pulled out of the RWC with the help of a thread in the foam. This way the feed point is never required to be opened. The RWC along with the sample is shown in Figure 5.3. A sharp resonance is required for accurate measurement, which is achieved with the help of a tuning screw in the RWC. The sample is placed in the center of the cavity which is operated in the $TE_{10s}$ mode for the electrical properties. Numerous challenges were encountered:

1. The resonance is very sensitive to the tuning screw. A slight movement affects the resonance strength and frequency, making accurate measurements impossible with this setup.

2. Very small and uniform sample preparation is difficult as the ferrite LTCC material is quite brittle, leading to frequent breakage during preparation and positioning of the ferrite.

3. The manual placement of the sample fouls the measurements. A slight variation in the placement produces different results. With this technique the measurements

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are not repeatable. A custom jig would need to be developed to keep the sample more accurately in place.

4. The thread position and size also affects the measurements. Again, a custom jig would be required to insert/remove the sample without threads.

On the basis of the above, useful microwave characterization of the ferrite under magnetic bias could not be performed. Nonetheless, the microwave characterization carried out under zero bias, and the magnetostatic characterization described in the following section, enabled development of preliminary working SoP devices.

![Figure 5.3 Setup for microwave characterization under biased conditions](image)

### 5.1.3 Magnetostatic Characterization

Magnetostatic characterization is done through hysteresis measurements. These measurements allow the extraction of important ferrite characteristics such as the relative permeability, saturation magnetization, squareness and coercivity. The hysteresis curve
(magnetic flux density $B$ versus magnetic field $H$), should be measured at DC but it is also acceptable in the lower frequency range. The 1 kHz test circuit used to perform magnetostatic characterization is shown in Figure 5.4 and it employs embedded transformers built in the ferrite under test. The primary side of the transformer is connected to an oscillator followed by an audio power amplifier to provide variable current to the winding. The series resistor $R_3$ has a value of 3.5 $\Omega$ and is used to measure the voltage $V_H$ across it. The voltage $V_H$ is directly proportional to the magnetic field $H$ inside the transformer core and it is applied to the horizontal deflection of an oscilloscope.

It is easily shown that the voltage at the output of the integrator is directly proportional to the magnetic flux density $B$ in the core, and this voltage is applied to the vertical deflection of the oscilloscope. The desired hysteresis curve can be viewed directly on the oscilloscope by plotting $V_v$ versus $V_H$.

![Figure 5.4 Magnetic hysteresis measurement test circuit.](image)

Two different types of transformers have been designed for this work. A straight solenoid transformer completely embedded within the ferrite LTCC material under test was first
designed, similar to previous work [89]. The front cross-sectional view of a unit cell is shown in Figure 5.5 (a). The turns are made of 200 μm wide silver conductors that are connected to the top and bottom conductors through 150 μm diameter vias, and the pitch between conductors is 375 μm. Each unit cell is comprised of 7 primary turns and 3 secondary turns. The complete transformer fits into a 10 layer thick ferrite LTCC module with each layer being 124 μm thick. In order to fit the solenoid transformer in a maximum permissible part size of 20 mm × 20 mm, 11 unit cells are used. The complete solenoid employs 77 primary and 33 secondary turns which required 1198 transitions and 1108 vias in all.

A finite-length solenoid is subject to end-effects which can introduce errors in the measurements. Further, leakage out of the sides of the solenoid is also a concern, which can potentially lead to overestimates of the flux inside its core. A toroid, on the other hand, entirely encloses the magnetic fields within its core and is less prone to leakage effects. A toroid transformer has therefore also been designed in which unit cells are closely spaced and the fields are more tightly contained within the windings, as shown in Figure 5.5 (b). The 112 primary turns and the 48 secondary turns are completely embedded in 10 ferrite LTCC layers. The inner diameter of the toroid transformer is 10.3 mm and the outer diameter is 18.7 mm. It has 16 unit cells which are spaced at 171 μm on the inner side and 1.28 mm at the outer side. The top view of one of the fabricated layers (before firing of LTCC) of solenoid and toroid are shown in Figure 5.5 (c) and (d) respectively.
The measurement procedure consists of incrementing the primary current periodically and recording the corresponding $V_H$ and $V_v$ voltages which are then converted to actual values of $H$ and $B$, respectively. The results are then plotted to obtain the $B(H)$ curves for every current setting. The major $B(H)$ curve, which was obtained at saturation using the solenoid transformer, is shown in Figure 5.6 by a dotted line.
Figure 5.6 Measured hysteresis curves from the LTCC transformers.

The major hysteresis loop was obtained by energizing the primary winding with a peak current of 650 mA. Based on the solenoid measurements, the saturation flux density $B_s$ is 330 mT for an applied magnetic field of 2100 A/m. The remanent flux density $B_r$ is 180, the squareness is 0.55, and the coercive magnetic field $H_c$ is 520 A/m. The same procedure was used for the toroid. Due to the curvature of the toroid, the resulting turn density of the primary winding of the toroid is lower than that of the solenoid by a factor of 0.6. The maximum $B(H)$ curve for the toroid, is shown in Figure 5.6 by a solid line.

A comparison of the curves in Figure 5.6 and the results obtained from the toroid indicate that ESL 40012 is easier to magnetize than it would appear to be with the solenoid. This is expected since the toroid suffers from less leakage effects than the solenoid. This difference is clearly evident in Figure 5.7, which plots the peak B field versus the peak H field for each
current setting. Although saturation could not quite be achieved with the toroid, the trend clearly indicates that the saturation magnetization $B_s$ approaches 400 mT instead of the 330 mT obtained using the solenoid. For the toroid, $B_r = 250$ mT, the squareness is approximately 0.63, and $H_c \approx 330$ A/m.

The results of Figure 5.7 may be used to calculate the linear permeability of the material. For any given operating point, the linear permeability $\mu_{lin}$ is the slope of the line that extends from the origin to that operating point. The resulting curves for the solenoid and the toroid are shown in Figure 5.8. The maximum $\mu_{lin}$ of 205 is achieved for an H-field of 715 A/m for the solenoid, whereas it is estimated to be 370 at an H-field of 430 A/m for the toroid.

![Graph showing measured peak B versus peak H for ESL 40012 LTCC.](image)

Figure 5.7 Measured peak B versus peak H for ESL 40012 LTCC.
5.1.4 Discussion

A number of important observations can be made based on the microwave and magnetostatic measurement results obtained thus far. The value of $\varepsilon_r$ (13.7) falls in the range of typical microwave substrates useful for circuit and antenna designs. In the unbiased state, the measured loss tangents of the ferrite are quite low ($4 \times 10^{-3}$) and decrease with frequency. Since the guided wavelength is a function of both $\varepsilon_r$ and $\mu_r$, this will help miniaturize antenna and passive elements design.

In the biased state, the high value of $B_s \approx 400$ mT indicates that a large degree of magnetic control can be achieved with ESL 40012, which is beneficial for the design of in-package
reconfigurable and tunable microwave components. The measured results also indicate that the remanent magnetization is sufficient to yield practical nonreciprocal devices operating at remanence. The measured high values of $\mu_{\text{lin}}$ also indicate that high Q inductors and transformers can be manufactured with this material. These results are encouraging as far as the implementation of microwave components in ferrite SoP is concerned.

5.2 Tunable antennas

Most of the previous ferrite based antennas are tuned to operate in the magnetically saturated state. Given that they are fabricated on traditional ferrite substrates, large external magnets (permanent or electro-magnets) must be used to provide the high magnetostatic fields. Such magnets are bulky and impractical given that 1) the substrates must operate in saturation and 2) the external fields are commensurate with the demagnetization factors of the substrates. This has typically required an external magnetic field intensity $H$ on the order of 80 000 A/m (1000 Oe) and makes the resulting system extremely bulky and unsuitable for the compact SoP approach. The designs presented in this chapter use a tunable patch antenna that is fabricated on a multilayer ferrite LTCC substrate with a completely embedded bias winding. Demagnetization factors are largely absent from such an arrangement, which greatly lowers the magnetostatic field strength required for tuning. Additionally, these antennas operate at a high enough frequency such that low-field losses are negligible, implying that unsaturated ferrite regions within the LTCC substrate are tolerable, which further serves to reduce the required magnetostatic field strength. This novel approach enables tuning of the antenna with field strengths on the order of 2000 to 4000 A/m (25-50 Oe).
5.2.1 Theory

Ferrite-based antennas typically use a variable magnetostatic bias to achieve tuneability and reconfigurability [130][131]. For such antennas, the resonance frequency variation is dependent on the bias direction and strength [132]. Usually, ferrite materials at microwave frequencies are used in the saturated state. In this regime, the well-established Polder equations [129] can be used to represent the permeability of ferrite in terms of applied magnetostatic field \( H_0 \) and saturation magnetization \( M_s \). These equations indicate that the elements of the permeability tensor exhibit a resonance around a specific frequency, called Larmor frequency \( f_0 \), which is dependent on \( H_0 \). Ferrite is very lossy in the vicinity of its Larmor frequency, thus it is customary to operate the ferrite above this frequency for microwave applications, even though the ability to tune the ferrite decreases with frequency in this range [128]. Previous characterization efforts have revealed that an internal H-field of over 2500 A/m is required to fully saturate ESL 40012 ferrite LTCC to its magnetization value of \( \mu_0 M_s = 0.4 \) T. Providing such high, uniform bias fields within a miniature LTCC package is quite challenging without the use of an external magnet. Failure to fully saturate the ferrite results in additional low-field losses, which are incurred up to approximately the magnetization frequency \( f_m = (2.8 \times 10^{10} \text{ Hz/T}) \cdot \mu_0 M_s = 11.2 \) GHz for this particular ferrite material. For consistentency with the SoP work presented in this thesis so far, the initial plan was to design ferrite LTCC based antennas for the 5 GHz band. Given the unlikelihood of achieving uniform bias and eliminating the low field losses (see the 2-9 GHz band in Figure 5.2), an operating frequency of 12 GHz was chosen [20].
Due to their anisotropic behavior, ferrites show different properties depending on the orientation of $H_0$ with respect to the direction of both the wave propagation and the RF magnetic field. Two different orientations of patch antennas are investigated here with respect to $H_0$, as shown in Figure 5.9. In the first case, the antenna is placed in a longitudinal orientation with respect to $H_0$ whereas in the second case, $H_0$ is perpendicular to the resonant dimension of the patch antenna (transverse to the RF propagation). According to Pozar, the second case should be more sensitive to the applied bias fields [92].

In the proposed design, the ferrite underneath the patch antennas will be partially biased using embedded electromagnet windings. Such internal windings do not suffer from demagnetization factors as do external bias field sources. Magnetostatic simulations have revealed that the a relatively low DC current of no more than 500 mA is sufficient to generate magnetic field strengths ranging from 2000 to 4000 A/m (25-50 Oe) within the core of the windings [20]. Tunability of the antenna will be achieved by varying the current flowing through the windings. This methodology has been used successfully in previous work for ferrite [20].
5.2.2 Antenna Design

For proof of concept, a microstrip patch antenna designed to operate at 12 GHz has been fabricated over the existing ferrite LTCC substrates with embedded windings that were used for material characterization. The cross-sectional view of the tunable antenna is shown in Figure 5.10. The module consists of a 10 layer thick ferrite LTCC ($h_1=1.09\text{mm}$) out of which the biasing windings occupy the bottom eight layers ($h_2=0.87\text{mm}$). The patch antennas made of copper
metallization are realized on the top of the substrate, while the ground plane is placed beneath the substrate.

Two slightly different antenna designs (small indented patch and large slotted patch) are investigated in different orientations as shown in Figure 5.11. The basic microstrip fed indented patch antenna is placed either in a longitudinal (Figure 5.11 d) or transverse orientation (Figure 5.11 b) with respect to the underlying solenoid bias winding. In one of the variations, the same antenna has been placed in a corner, slightly away from the solenoid winding (Figure 5.11 e). The same antenna has also been placed on toroidal transformer, as shown in Figure 5.11 (a).

The second antenna design consists of a large slotted patch antenna that operates in its 3\textsuperscript{rd} resonance at 12 GHz (Figure 5.11 c). It has been designed with a slot in the center in order to increase its electrical length and fit it in the available substrate space.
Figure 5.11 Fabricated antennas on ESL 40012 ferrite LTCC (a) small patch on toroid (b) transverse small patch on solenoid (c) large patch with slot on solenoid (d) longitudinal small patch on solenoid (e) longitudinal small patch placed in the corner with a microstrip line

5.2.3 Tunable Patch Impedance Measurements and Discussion

The measurement setup employed for obtaining the antenna’s input impedance is shown in Figure 5.12. It consists of a universal jig to feed the patch antenna and record the s-parameters through a network analyzer. The embedded underlying winding is biased through DC probes and pads on the top layer connected to a variable power supply.
The antennas are measured under both zero bias and biased conditions. For the latter case, current is increased in steps of 50 mA until the maximum value of 500 mA for the solenoid winding and 700 mA for the toroid winding. The solenoid winding exhibits a measured series resistance $R_s$ of 5 $\Omega$, whereas the toroid demonstrates $R_s$ of 5.8 $\Omega$. The measured results for the small transverse antenna (Figure 5.11 b) on the solenoid are shown in Figure 5.13 (a). The 12 GHz resonance, highlighted with a circle in Figure 5.13 (a) has been expanded for clarity in Figure 5.13 (b) showing intermediate bias steps. A very large tunability of the resonance frequency is observed with varying magnetic bias. The other structures of Figure 5.11 exhibited less tunability.

Figure 5.12 Tuneable antenna measurement setup
Figure 5.13 Measured Results (a) 9-15 GHz range (b) zoomed in at 12 GHz range
Figure 5.13 (b) reveals that the maximum tunability is 550 MHz around 12 GHz achieved for the transverse orientation with respect to the solenoid winding. In this orientation the bias magnetic field is transverse to the resonant direction of the patch. The resonant frequency for this orientation decreases with the bias. This is consistent with the results in [92] which show maximum tuning for similar orientation. This result is quite encouraging keeping in mind that the antenna structure employs a non-optimized bias network. The multiple dips in the measured results are also attributed to the embedded windings. When the same antenna is placed in the longitudinal orientation with respect to the bias magnetic field (shown in Figure 5.11 d), the tuning range reduces to approximately 300 MHz around 12 GHz. It is also observed that if the same antenna is in the corner of the substrate (antenna partially covers the winding as shown in Figure 5.11 (e) the tuning range reduces to approximately 200 MHz. The large patch antenna with slot (shown in Figure 5.11 c) displays a tuning range of 500 MHz. This tuning range is achieved with the antenna placed in a longitudinal orientation with respect to the bias field. It is believed that if the antenna with the slot is placed in the transverse orientation with respect to \( H_0 \), it will provide a tuning range in excess of 500 MHz. Lastly, the small antenna on a substrate with toroid transformer (shown in Figure 5.11 a) showed a tuning range of 200 MHz for the same or slightly higher bias field as compared to the solenoid biased antennas. This agrees well with the hysteresis measurements because the toroid transformer shows maximum fields to be confined within the windings and the leakage fields are considerably reduced as compared to the solenoid. It is clear that the antennas used herein are not only responding to the magnetic flux within the core of the transformers, but also to the leakage flux lines around the cores of the transformers (flux return paths). This proof of concept
has re-used transformer cores that were previously used to characterize the ferrite. As such, the windings have not been optimized for antenna-specific tuning. Despite this, good tuning ability is observed for the aforementioned antennas, albeit for high bias currents. For 500 mA of bias current in a bias winding with $R_s = 5 \, \Omega$, requires 2.5 V of voltage drop and results in 1.25 watts of power consumption. Though the power consumption seems high, it is in the acceptable range if the current does not have to be supplied continuously. For practical ferrite based circuits, the bias current has to be provided for very short period of time as ferrite holds its magnetization in remanence. This means that the circuits tuned to discrete points through applied bias can hold on to their state even if the bias current is removed. Moreover, substantial reductions of bias current are expected if the bias windings and their placement are optimized for antenna applications.

In order to optimize the tuning range, there must be enhanced interaction between the RF magnetic field of the patch antenna and dc bias magnetic field. Despite the need of placing the antennas close to strong bias field zones, i.e. close to the windings, practically it becomes difficult due to the interference of RF fields with these windings. A stronger perturbation is experienced in the case when the microstrip feed line is placed on the windings (see Figure 5.11c and Figure 5.11d). This strong perturbation suggests that the microstrip feed lines are very sensitive to the presence of embedded windings. This fact must be carefully considered in tunable antenna designs on substrates with embedded windings.
5.2.4 Antenna Gain and Radiation Pattern Measurements

A challenging part of characterizing the ferrite based tunable antennas is measuring its gain and radiation pattern under biased conditions. This is because the antennas have to be mounted and rotated in the anechoic chamber along with the DC probes which are required to provide biasing to the windings underneath the antenna. A custom jig has been made for this purpose as shown in Figure 5.14. The DC probes are mounted on a metallic plate and then this plate is screwed to the base plate in the anechoic chamber. The microstrip based universal test jig has also been screwed to the base plate. The antennas are fed through the universal test jig and biased through the probes. A horn antenna acted as a transmit antenna on the other end. It is observed that at certain angles the probes blocked the radiation pattern measurement. However, the testing is not affected by the presence of the probes in most of the measurement scans. This fact is established by doing two sets of measurements, one with and the other without the probes. The measurements are preceded by the calibration procedure which is done through two horn antennas for the 11-13 GHz frequency range.

Figure 5.14 Ferrite antenna gain and radiation pattern measurement setup
The measured gain and E-plane radiation pattern for the transverse patch on the solenoid is shown in Figure 5.15 under bias and unbiased conditions. A maximum gain of approximately 2 dB is measured at 12.5 GHz. The low gain value and the variation of the radiation pattern at various angles are attributed to the presence of strong surface waves which radiate from the edges of the substrate. These surface waves are expected due to the high permittivity of the thick LTCC substrate. As was the case with the impedance measurements, the parasitic influence of the windings within the substrate is apparent in the measured radiation pattern.

With little variation in the radiation pattern for the unbiased and biased conditions (see Figure 5.15), tunable antenna performance can be controlled with ease. It is worth mentioning here that the gain has been corrected for mismatch loss due to varying bias levels. Measurements of the large antenna with the slot suffered the most due to severe blockage from the probes, mount and jig. The radiation pattern from the toroid based antennas appeared to be the cleanest and resembled the typical patch antenna pattern; however the gain values are slightly lower. This further confirms the power lost due to surface waves as toroid substrates are larger in terms of area as compared to the solenoid substrates.
5.3 Ferrite LTCC SoP Implementations

Based on the measured results, the concept of ferrite LTCC tunability can be applied to SoP modules that extend beyond antennas. The possible extension of this work applicable to antennas and other SoP components can be summarized as follows.

5.3.1 Antennas

The performance of ferrite LTCC based antennas can be considerably improved by co-design of antenna and the underlying winding. In order to optimize the tuning range, this co-design of antenna and bias network must enhance the interaction of antenna RF magnetic field and the dc bias magnetic field. To reduce the interference from the bias winding, the design must be optimized in terms of size of the winding and its placement with respect to the antenna. New configurations for the bias winding must also be explored. Similarly, it is expected that alternate
radiators like CPW patch and slot antennas can also reduce the perturbation from the bias winding. In order to maximize the efficient use of the 3D substrate, radiators like Dielectric resonator antennas (DRAs) and helical antennas can also be employed.

5.3.2 Reflectarray

Though not shown here, microstrip line measurements under varying bias conditions demonstrated strong phase change capability. Also, it is well known that patch antennas whose resonant frequencies change with magnetic bias also exhibit strong phase change of the radiated wave. Therefore ferrite LTCC based patch antennas are ideal candidates for reconfigurable reflectarrays.

5.3.3 Other tunable circuits

Several possibilities exist for tunable microwave components within a ferrite LTCC SoP. For instance, Figure 5.16 shows the attenuation constant of a microstrip line placed above the bias winding of Figure 5.5 (c). Though the transmission is affected by the interference from the underlying winding, it can be seen that over a narrow frequency band in which the combined microstrip/winding structure is resonant, the line’s propagation losses vary by 10 dB/cm with magnetic bias. Such a result proves the feasibility of distributed tunable switching, phase shifting and filtering circuits. Similarly, lumped element realizations of these components would also be tunable if an inductor is employed. For example an embedded tunable filter or matching network can be built inside the bias winding to make use of the high magnetic field intensity.
The measured results are encouraging as far as the implementation of tunable microwave components in ferrite SoP is concerned. The low loss material property makes it an attractive substrate for in-package passive element design in the microwave frequency range. However, the true advantage of ferrite LTCC is its ability to change its permeability tensor with applied magnetic bias, thereby giving an additional dimension of freedom to microwave designers.

![Figure 5.16 Ferrite microstrip line measured attenuation constant](image)

**Figure 5.16 Ferrite microstrip line measured attenuation constant**

### 5.4 Ferrite based Tunable RF SoP Design Issues

Following the experimental work done in this chapter, it is important to highlight the major challenges and issues involved in advanced ferrite based tunable RF SoP development. These points will be useful for continued research on the topic.
1. The layout of the solenoid and toroid transformers is very complex and requires extremely large CAD tool memory. The module must be broken into individual unit cells which are then repeated to realize the complete winding.

2. The magnetostatic measurements performed using embedded LTCC transformers are quite challenging as they require high currents. Special arrangements are required to cool off the modules to avoid the burning of the embedded windings. Also the current is passed in very short intervals of time to avoid overheating of the modules.

3. Microwave measurements under the biased state required very small size ferrite LTCC samples to be placed very accurately at specific locations in the waveguide. The precision required was beyond the manual placement of the samples and hence resulted in non-repeatable measurements. A custom jig is required to accurately place the sample in the waveguide. The setup also required large electromagnets to overcome the demagnetization fields.

4. The tunable antennas employ the same transformers which are used to characterize the material to avoid expensive fabrication costs. These are far from optimum for antenna design but do serve to prove the concept.

5. Ansoft HFSS has many limitations with respect to modeling the ferrite based designs. In this tool, the magnetized state of a ferrite material can be specified with the value of $M_s$. The direction and value of $H_0$ are also important parameters for the simulation model. The distribution of the DC-bias field inside the ferrite is usually assumed to be uniform. Another approximation which HFSS makes is that the ferrite is always operating in its
saturation state. It is worth mentioning here that HFSS has the ability to define a diagonal non-linear permeability tensor (B-H curve), however this property cannot be used for ferrite modelling due to the simulator's inability to employ the non-diagonal elements of the permeability tensor. Due to the simulator's limitation, most of this work relied on experimental verifications. Other simulators like CST microwave must be employed in future investigations.

6. Radiation measurements of these antennas over embedded windings are very difficult as they require the dc biasing through the probes at the same time as the antennas are being rotated and measured for RF power. A custom jig has been made for it as shown in Figure 5.14.

7. Due to the inability to perform RF measurements in the active region of the windings (embedded in the substrate), it was hard to assess the remanent magnetization in the biased microwave state. For future attempts, a strip line structure may provide better prediction of the residual magnetic fields.

8. The microstrip line mode was subjected to strong interference from the embedded windings, hence the measurements could not provide very clear results about phase tuning with respect to the applied bias.

9. Finally, for the same reason as mentioned in point 6, it was difficult to assess whether or not the low field losses disappear for the biased state.
5.5 Summary and Contributions

ESL 40012 experimental ferrite LTCC tape has been characterized for its microwave and magnetostatic properties. Microwave measurements performed at 9.86 GHz and 27.2 GHz reveal an \( \varepsilon_r \) value of 13.6 and tan\( \delta \) values of 0.004 and 0.001. Novel embedded LTCC transformers have been used to measure the magnetostatic properties. These measurement results show that \( B_s \) is nearly 400 mT for an applied magnetic field approaching 2000 A/m. The remanent flux density \( B_r \) is 250 mT, the squareness is 0.63, and the coercive magnetic field \( H_c \) is 430 A/m.

For the first time, ferrite Low Temperature Co-fired Ceramic (LTCC) tunable antennas are presented that operate in the ferrite's partially-biased state. These antennas are frequency tuned by the magnetostatic field produced in a winding that is completely embedded in the ferrite LTCC substrate. Due to the embedded windings, the typically required magnetic bias (of the order of 1000 Oersted) for antenna tuning has been reduced by 95% (to the order of 50 Oersted). The fact that large electromagnets are not required for tuning makes ferrite LTCC with embedded bias windings an ideal platform for advanced tunable System-on-Package (SoP) applications. Measurements reveal a tuning range of 550 MHz in the 12 GHz band for a single microstrip patch antenna on a ferrite LTCC substrate. Two different biasing structures and their effect on the antenna performance are discussed. The effect of antenna position and orientation with respect to the biasing winding is also investigated. Finally, the antenna radiation characteristics are compared under biased and unbiased conditions. An antenna gain of 2 dB is measured. These results constitute the fourth and fifth contributions of the thesis, namely 'Ferrite LTCC Material Characterization' and 'Ferrite LTCC Based Antennas for Tunable SoP'.

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The work in this chapter has resulted in a conference paper [20]. A journal paper has recently been submitted [21].
6 Conclusions and Future Work

This chapter summarizes the research work and the contributions of this thesis and proposes future work which will help researchers to advance the art of RF SoC and SoP design.

6.1 Conclusions

Chapter 3 has presented three novel SoC designs having on-chip antennas combined with RF transmitter and receiver circuitry. A highly integrated, low power CMOS VCO TX has been demonstrated for short range wireless radiation sensor applications. The VCO tank inductor has been optimized to act as an on-chip inductor-antenna, thus minimizing chip area. Its $0.5\text{mm}^2$ size is the smallest reported on-chip antenna in the UN II band. This is the first ever demonstration of experimental characterization of an on-chip inductor/antenna for its radiation properties. The tradeoffs in the design and challenges in the experimental work have been highlighted. The complete TX chip sized $1.5\text{mm}^2$ consumes 3.3 mW of power and can communicate with a low noise receiver connected to a patch antenna 2 m away from the TX. With the integration of a suitable power source, the complete wireless dosimeter can be
smaller than a dime as shown in Figure 3.22. On the RX side, co-design of on-chip dipole antenna and LNA has been demonstrated for conjugate matching. These results represent the first contribution of this thesis, namely ‘Oscillator TX with On-chip Inductor/Antenna’.

The work of this chapter has led to many publications. One journal [9] and seven conference papers have already been published [11-15][17][18]. One more journal paper has been accepted recently [23].

Two RF SoP designs suitable for wireless biomedical applications have been presented in chapter 4. A novel LTCC based TX SoP implementation has been demonstrated which makes use of on-chip-antenna-to-LTCC-package antenna coupling through an aperture in the common ground plane. The strategy is useful as it eliminates the need for isolating buffers, bond pads, bond wires, matching elements, baluns and transmission lines. It not only reduces the number of components and simplifies SoP design but also consumes lower power. The chip coupling to LTCC patch antenna improves the TX module gain by 32 dB (in simulation) and range by 22 m as compared to the on-chip antenna alone, without affecting the RF circuit performance and power consumption. The conventional LTCC package provides 3 times more range than the proposed design but consumes 12 times more power. To the author’s knowledge, this is the first ever LTCC aperture coupled patch antenna implementation with direct feeding from a TX on-chip antenna. A simple analytical method is described to model the new coupling between the on-chip antenna and the slot in the ground plane. The work in chapter 4 completes the second and third contributions of the thesis, namely ‘LTCC SoP Design’ and ‘Novel LTCC SoP Analytical Model’.
The work in chapter 4 has resulted in one journal paper [10] and a conference paper [19]. Another journal paper has recently been submitted [22]. The conference paper [19] won the 'overall best paper prize' in European Wireless Technology Conference (EuWiT) at European Microwave Week in Amsterdam [124]. The demonstration of conventional LTCC TX module won the national technology innovation competition during the Canadian Microelectronics Texpo [125].

ESL 40012 experimental ferrite LTCC tape has been characterized for its microwave and magnetostatic properties in chapter 5. Microwave measurements performed at 9.86 GHz and 27.2 GHz reveal an $\varepsilon_r$ value of 13.6 and $\tan\delta$ values of 0.004 and 0.001. Novel embedded LTCC transformers have been used to measure the magnetostatic properties. These measurement results show that $B_s$ is nearly 400 mT for an applied magnetic field approaching 2000 A/m. The remanent flux density $B_r$ is 250 mT, the squareness is 0.63, and the coercive magnetic field $H_c$ is 430 A/m.

For the first time, ferrite Low Temperature Co-fired Ceramic (LTCC) tunable antennas are also presented in chapter 5, that operate in the ferrite's partially-biased state. These antennas are frequency tuned by the magnetostatic field produced in a winding that is completely embedded in the ferrite LTCC substrate. Due to the embedded windings, the typically required magnetic bias (of the order of 1000 Oersted) for antenna tuning has been reduced by 95% (to the order of 50 Oersted). The fact that large electromagnets are not required for tuning makes ferrite LTCC with embedded bias windings an ideal platform for advanced tunable System-on-Package (SoP) applications. Measurements reveal a tuning range of 550 MHz in the 12 GHz band for a single microstrip patch antenna on a ferrite LTCC substrate. Two different biasing
structures and their effect on the antenna performance are discussed. The effect of antenna position and orientation with respect to the biasing winding is also investigated. Finally, the antenna radiation characteristics are compared under biased and unbiased conditions. An antenna gain of 2 dB is measured. These results constitute the fourth and fifth contributions of the thesis, namely 'Ferrite LTCC Material Characterization' and 'Ferrite LTCC Based Antennas for Tunable SoP'.

The work in chapter 5 has resulted in a conference paper [20]. A journal paper has recently been submitted [21].

6.2 Future Work

Specific recommendations for future work were made in the “Design Issues” sections of chapters 3, 4 and 5. In addition the following research is proposed.

RF SoC Design

All measures were taken in this thesis to ensure an efficient on-chip antenna design, like increasing the metal width and placing it close to the edges of the chip. However it is very difficult to design an efficient on-chip antenna on low resistivity bulk silicon (10 Ω-cm). Though the on-chip antenna performance in terms of its communication range is satisfactory for this particular application, it must be enhanced for other applications. The antennas can be made efficient by employing high resistivity substrates, but this will 1) increase the cost and 2) make it a non-compatible substrate for the circuits.
One solution can be to make use of a hybrid process which can accommodate MEMS on conventional CMOS substrates. This has recently been offered by DALSA semiconductors. By virtue of this hybrid technology, the antenna can be realized as a MEMS structure away from the lossy Si substrate as shown in Figure 6.1.

![MEMS Antenna diagram](image)

**Figure 6.1 Proposed SoC in hybrid CMOS process (MEMS based)**

**RF SoP Design**

The future of SoP may well lie in hybrid packages with application specific layers as shown in Figure 6.2. These will employ ferrite layers for magnetically tuned elements and ferro-electric layers for electrically tuned circuits. Such futuristic SoP will employ flip chip dies with integrated MEMS structures. Also future SoP research will focus on flexible materials to realize state of the art wearable devices as shown in Figure 6.3.
In particular, ferrite LTCC can be a very good medium for tunable inductors which can be employed in filters, couplers and matching networks to make them tunable. The LTCC inductors can be realized right in the active region of the windings and hence much more tuning can be expected as compared to the antenna work reported in this thesis. Similarly, the winding can be placed inside the inductor to achieve high inductance values for low frequency switching.
applications. A potential application for the tunable matching elements is the cellular handset front end. In order to maintain the efficiency of the power amplifier for varying input power levels and load conditions, its matching network must always adapt to the optimum load. This could be achieved through ferrite LTCC based adaptive matching network as shown in Figure 6.4.

Figure 6.4 Ferrite LTCC based adaptive matching network
Bibliography


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